

I<sup>2</sup>C-Controlled 5A Buck or Boost Charger with NVDC Power Management and USB OTG for 2-Cell to 4-Cell Battery Pack Applications

#### DESCRIPTION

The MP2650 is a highly integrated buck or boost charger IC with narrow-voltage DC (NVDC) power path management and USB On-The-Go (OTG) for battery packs with 2 cells to 4 cells in series. All power MOSFETs are integrated to provide a compact system solution size.

The IC can accept a wide input voltage ( $V_{IN}$ ) range for charging, with a 21V maximum. The device has two operating modes during the charging process: boost charging mode and buck charging mode, depending on  $V_{IN}$  and the cell count.

With the I²C interface, the MP2650 can be flexibly configured to set the parameters in both charging mode and OTG mode. Parameters include the input current ( $I_{\rm IN}$ ) limit,  $V_{\rm IN}$  limit, charging current, battery charge voltage regulation, and safety charge timer. It can also provide the operation statuses through status and fault registers.

To guarantee safe operation, the IC limits the die temperature to a preset value of 120°C. Other safety features include input over-voltage protection (OVP), battery OVP, system OVP, thermal shutdown, battery temperature protection, and a configured timer to prevent prolonged charging of a dead battery.

To comply with IMVP8 specifications, the IC provides three analog output pins for system power (PSYS), input current (IAM), and battery current (IBM). It also has a processor hot indication pin (PROCHOT) for system power control.

NVDC power path management regulates the system voltage within a narrow DC range to provide an optimized system bus voltage for the rails at the system bus. With this feature, the system can continue operating even when the battery is completely depleted or removed.

The MP2650 is available in a QFN-30 (4mmx5mm) package.

4/22/2022

#### **FEATURES**

- Buck or Boost Charger for Battery Packs with 2 Cells to 4 Cells in Series
- All Switching MOSFETs are Integrated
- NVDC Power Management with an Integrated Battery FET
- 4V to 21V Operating Input Voltage (V<sub>IN</sub>) Range
- Up to 28V (20ns) Sustainable V<sub>IN</sub>
- Configurable V<sub>IN</sub> Limit
- Up to 5A Configurable Input Current (I<sub>IN</sub>)
   Limit (Up to 45W Total Power)
- Up to 5A Configurable Charge Current
- Configurable Battery Charge Voltage Regulation Up to 4.5V/Cell
- System Power Indication via the PSYS Pin
- I<sub>IN</sub> and Battery Current Monitoring via the IAM and IBM Pins
- Input Over-Voltage Protection (OVP), Battery Temperature Protection, Battery OVP, System OVP
- Configurable Safety Charge Timer
- Thermal Regulation and Thermal Shutdown
- 600kHz, 800kHz, 1MHz, or 1.25MHz Configurable Switching Frequency (f<sub>SW</sub>)
- Input Power Source Status Indication Pin
- I<sup>2</sup>C Interface to Support Flexible Parameter Control
- Comprehensive Fault and Status Reporting in Register
- Up to 5V/3A USB On-The-Go (OTG)
- Configurable OTG Output Current (I<sub>OUT</sub>)
   Limit
- Short-Circuit Protection (SCP) in OTG Mode
- Available in a QFN-30 (4mmx5mm) Package

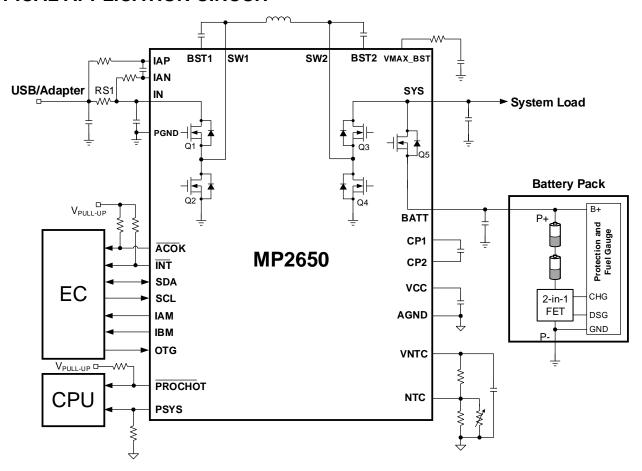
#### **APPLICATIONS**

- Tablets and Notebooks
- Bluetooth Speakers
- Portable Gimbals

All MPS parts are lead-free, halogen-free, and adhere to the RoHS directive. For MPS green status, please visit the MPS website under Quality Assurance. "MPS", the MPS logo, and "Simple, Easy Solutions" are trademarks of Monolithic Power Systems, Inc. or its subsidiaries.



## TYPICAL APPLICATION CIRCUIT





### **ORDERING INFORMATION**

Part Number*	Package	Top Marking	MSL Rating
MP2650GV-xxxx**			
MP2650GV-0200***	OEN 20 (4mmy5mm)	See Below	4
MP2650GV-0300****	QFN-30 (4mmx5mm)	See Delow	1
MP2650GV-0400*****			
EVKT-MP2650	Evaluation Kit	N/A	N/A

<sup>\*</sup> For Tape & Reel, add suffix -Z (e.g. MP2650GV-xxxx-Z).

\*\*\* "-0200" is configuration code for 2-cell applications.

\*\*\*\* "-0300" is configuration code for 3-cell applications.

\*\*\*\*\* "-0400" is configuration code for 4-cell applications.

#### **TOP MARKING**

**MPSYWW** 

MP2650

LLLLLL

MPS: MPS prefix Y: Year code WW: Week code MP2650: Part number LLLLL: Lot number

#### **EVALUATION KIT EVKT-MP2650**

EVKT-MP2650 kit contents (items below can be ordered separately):

#	Part Number	Item	Quantity
1	EV2650-V-01A	MP2650 evaluation board (MP2650GV-0200)	1
2	EVKT-USBI2C-02 bag	Includes one USB to $I^2C$ communication interface, one USB cable, and one ribbon cable	1
3	Online resources	Include datasheet, user guide, product brief, and GUI	1

#### Order directly from MonolithicPower.com or our distributors.

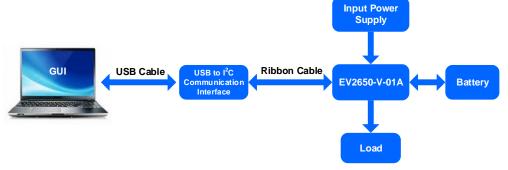
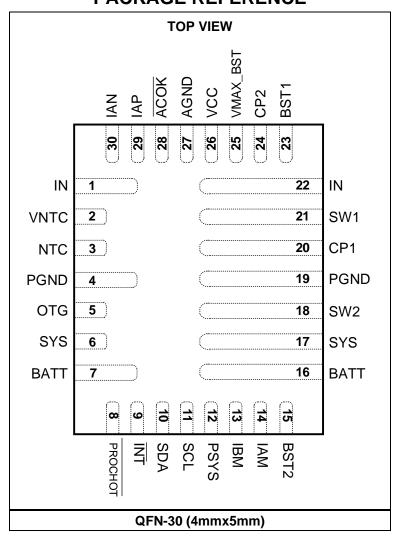


Figure 1: EVKT-MP2650 Evaluation Kit Set-Up

<sup>\*\* &</sup>quot;xxxx" is the configuration code identifier for the register settings. For the default case, the number is "-0000." Each "x" can be a hexadecimal value between 0 and F. Work with an MPS FAE to create this unique number, even if ordering the "-0000" code.



## **PACKAGE REFERENCE**





## **PIN FUNCTIONS**

Pin#	Name	Description
1, 22	IN	Power input pin. IN is the IC's power input from either an adapter or USB.
2	VNTC/ CMOUT	<b>Negative temperature coefficient (NTC) network pull-up voltage.</b> VNTC is the pull-up voltage of the NTC comparator resistor divider, which provides both the feedback and the reference. This pin can be also configured as an independent comparator output (CMOUT) via the I <sup>2</sup> C interface.
3	NTC/ BATDET	NTC thermistor input. Connect an NTC thermistor from the NTC pin to AGND. Configure the hot and cold temperature windows with a resistor divider connected from VNTC to NTC to AGND. Charging is suspended when NTC is out of its range. This pin can also be configured as a battery detection terminal via the I <sup>2</sup> C interface.
4, 19	PGND	Power ground.
5	OTG/ CMIN	<b>USB On-The-Go (OTG) enable control.</b> This pin can also be configured as the independent comparator input pin via the I <sup>2</sup> C interface. When this pin is configured to be CMIN, OTG is enabled via the internal register bit.
6, 17	SYS	System output. Connect 5 x $22\mu F$ ceramic capacitors from SYS to PGND, and place them as close as possible to the IC.
7, 16	BATT	Battery positive terminal. Connect 2 x 22µF ceramic capacitors from BATT to PGND, and place them as close as possible to the IC.
8	PROCHOT	<b>Processor hot interrupt output.</b> This pin is an open-drain structure. It is pulled to AGND when the PROCHOT signal asserts, and floats when a PROCHOT event is not occurring. This pin must be pulled up externally.
9	INT	<b>Open-drain interrupt output.</b> The INT pin can send the charging status and fault interrupt signals to the host. It must be pulled up externally.
10	SDA	I <sup>2</sup> C interface data line. Connect SDA to the logic rail through a 10kΩ resistor.
11	SCL	I <sup>2</sup> C interface clock line. Connect SCL to the logic rail through a 10kΩ resistor.
12	PSYS	<b>System power indication pin.</b> This pin outputs a current source that is proportional to the total system power.
13	IBM	<b>Battery current-sense output.</b> IBM outputs a voltage that is proportional to the battery charge current or battery discharger current.
14	IAM	<b>Input current-sense output.</b> IAM outputs a voltage that is proportional to the input current.
15	BST2	<b>Bootstrap for boost phase</b> . Connect a 470nF bootstrap capacitor between the BST2 and SW2 pins to form a floating supply across the power MOSFET driver. This drives the power MOSFET's gate above the supply voltage.
18	SW2	Boost phase switching node.
20	CP1	Charge pump node 1. Place a 470nF capacitor between the CP1 and CP2 pins.
21	SW1	Buck phase switching node.
23	BST1	<b>Bootstrap for buck phase.</b> Connect a 470nF bootstrap capacitor between the BST1 and SW1 pins to form a floating supply across the power MOSFET driver. This drives the power MOSFET's gate above the supply voltage.
24	CP2	Charge pump node 2. Place a 470nF capacitor between the CP1 and CP2 pins.
25	VMAX_BST	<b>Charge pump output.</b> Connect a 100nF ceramic capacitor in series with a $100\Omega$ resistor from VMAX_BST to PGND, and place the capacitor and resistor as close as possible to the IC.





## PIN FUNCTIONS (continued)

Pin #	Name	Description
		VCC LDO output. VCC can provide 3.6V/50mA for internal circuits, as well as the pull-
26	VCC	up voltage for the open-drain pins (ACOK, INT, and PROCHOT). Connect a 10μF ceramic capacitor from VCC to AGND, and place it as close as possible to the IC.
27	AGND	Analog ground.
28	ACOK	<b>Input power present indication.</b> This pin is an open-drain structure, and must be pulled up externally.
29	IAP	Input current-sense positive terminal.
30	IAN	Input current-sense negative terminal.

#### **ABSOLUTE MAXIMUM RATINGS (1)**

IN, IAN, IAP to PGND (20ns)0	.3V to +28V
IN, IAN, IAP to PGND (DC)0	.3V to +26V
SYS to PGND0	.3V to +24V
VMAX_BST to PGND	0V to 26V
BATT to PGND0	.3V to +24V
SW1 to PGND (20ns)	-2V to +28V
SW1 to PGND (DC)0	.3V to +24V
SW2 to PGND0.3V (-2V for 20	
CP1 to PGND (DC)0	
BST1 to PGNDSW1 to	o SW1 + 5V
BST2 to PGNDSW2 t	
CP2 to PGND CP1	to CP1 +5V
All other pins to AGND	0.3V to +5V
Continuous power dissipation ( $T_A = 1$	25°C) <sup>(2)</sup>
	3.29W
Junction temperature	
Lead temperature (solder)	260°C
Storage temperature65°C	

#### ESD Ratings

Human body model (HE	3M)	2000V
Charged device model (	(CDM)	)750V

### Recommended Operating Conditions (3)

Supply voltage (V <sub>IN</sub> )	4V to 21V
Input current	Up to 5A
Charge current	Up to 5A
Discharge current via battery FET	Γ (DC)
	Up to 14A
Battery voltage	Up to 18V
Operating junction temp (T <sub>J</sub> )4	10°C to +125°C

#### 

#### Notes:

- 1) Exceeding these ratings may damage the device.
- 2) The maximum allowable power dissipation is a function of the maximum junction temperature,  $T_J$  (MAX), the junction-to-ambient thermal resistance,  $\theta_{JA}$ , and the ambient temperature,  $T_A$ . The maximum allowable continuous power dissipation at any ambient temperature is calculated by  $P_D$  (MAX) =  $(T_J$  (MAX)  $T_A)$  /  $\theta_{JA}$ . Exceeding the maximum allowable power dissipation can produce an excessive die temperature, and the regulator may go into thermal shutdown. Internal thermal shutdown circuitry protects the device from permanent damage.
- The device is not guaranteed to function outside of its operating conditions.
- 4) Measured on JESD51-7, 4-layer PCB.



## **ELECTRICAL CHARACTERISTICS** (5)

 $V_{IN} = 5V$ ,  $V_{BATT} = 3.7V/cell$ , RS1 =  $10m\Omega$ ,  $T_A = 25^{\circ}C$ , unless otherwise noted.

Parameter	Symbol	Condition	Min	Тур	Max	Units
Input Voltage (V <sub>IN</sub> ) Characteri	stics					
V <sub>IN</sub> under-voltage lockout (UVLO) threshold	V <sub>IN_UVLO</sub>	V <sub>IN</sub> falling	3.45	3.68	3.87	V
V <sub>IN</sub> UVLOhysteresis		V <sub>IN</sub> rising		350		mV
V <sub>IN</sub> UVLO recovery deglitch time		V <sub>IN</sub> rising		30		ms
V <sub>IN</sub> power-on reset (POR)	V <sub>IN_POR</sub>	V <sub>IN</sub> rising		3.17		V
V <sub>IN</sub> POR hysteresis		V <sub>IN</sub> falling		620		mV
V <sub>IN</sub> over-voltage lockout (OVLO) threshold	V <sub>IN_OVLO</sub>	V <sub>IN</sub> rising	23	24	25	V
V <sub>IN</sub> OVLO hysteresis		V <sub>IN</sub> falling	1.55	1.66	1.78	V
DC/DC Converter						
Input shutdown current	I <sub>SHDN</sub>	V <sub>IN</sub> = 5V, Q1–Q4 are off			9.5	mA
input shutdown current	ISHDN	V <sub>IN</sub> = 20V, Q1–Q4 are off			9.5	mA
VCC LDO output voltage	V <sub>VCC</sub>	$V_{IN} = 5V$ , $I_{VCC} = 10mA$	3.4	3.6	3.73	V
VCC LDO current limit	Ivcc	$V_{IN} = 5V$ , $V_{BATT} = 7.8V$	50			mA
IN to SW1 N-channel MOSFET (Q1) on resistance	Ron_Q1			16		mΩ
SW1 to PGND N-channel MOSFET (Q2) on resistance	R <sub>ON_Q2</sub>			16		mΩ
SW2 to SYS N-channel MOSFET (Q3) on resistance	R <sub>ON_Q3</sub>			6		mΩ
SW2 to PGND N-channel MOSFET (Q4) on resistance	R <sub>ON_Q4</sub>			16		mΩ
SYS to BATT N-channel MOSFET (Q5) on resistance	R <sub>ON_Q5</sub>			11		mΩ
Battery tracking regulation voltage	VTRACK		5			mV
Minimum system regulation voltage	Vsys_reg_min	2 cells, REG07h, bits[5:4] = 01, REG30h, bit[3] = 0	5.97	6.16	6.34	V
		REG0Bh, bits[4:3] = 00		600		
Operating frequency		REG0Bh, bits[4:3] = 01		800		IzU=
Operating frequency	fsw	REG0Bh, bits[4:3] = 10		1000		kHz
		REG0Bh, bits[4:3] = 11		1250		
System short-circuit entry threshold		Boost charge, V <sub>SYS</sub> falling, compare to V <sub>IN</sub>	30	168	320	mV
System short-circuit exit threshold		Boost charge, V <sub>SYS</sub> rising, compare to V <sub>IN</sub>	110	314	500	1117



 $V_{IN}$  = 5V,  $V_{BATT}$  = 3.7V/cell, RS1 = 10m $\Omega$ ,  $T_A$  = 25°C, unless otherwise noted.

Parameter	Symbol	Condition	Min	Тур	Max	Units
Battery Charger						
Battery charge voltage regulation		2 cells, default: 8.4V (REG04h, bits[6:1] = 100111, REG07h, bits[7:6] = 00)	8.337	8.40	8.463	V
	Vbatt_reg	3 cells, default: 12.6V (REG04h, bits[6:1] = 100111, REG07h, bits[7:6] = 01)	12.465	12.59	12.715	V
		4 cells, default: 16.8V (REG04h, bits[6:1] = 100111, REG07h, bits[7:6] = 10/11)	16.613	16.78	16.947	V
		Icc = 3A, REG02h, bits[6:0] = 0111100	2.8	3	3.3	Α
Fast charge current	Icc	Icc = 2A, REG02h, bits[6:0] = 0101000	1.85	2	2.2	Α
r ast charge current	icc	I <sub>CC</sub> = 1A, REG02h, bits[6:0] = 0010100	0.91	1	1.13	Α
		Icc = 0.5A, REG02h, bits[6:0] = 0001010	0.44	0.5	0.6	Α
Trickle charge to pre- charge threshold	V <sub>BATT_TC</sub>	2 cells, V <sub>BATT</sub> rising	3.92	4	4.25	V
Trickle charge to pre- charge threshold hysteresis		2 cells, V <sub>BATT</sub> falling	450	550	650	mV
Trickle charge current	I <sub>TC</sub>	2 cells, V <sub>BATT</sub> = 1V	60	100	190	mA
Thickie charge current	TIC	2 cells, V <sub>BATT</sub> = 3V	130	188	240	mA
Pre-charge to fast charge		2 cells, REG07h, bits[5:4] = 01, REG30h, bit[3] = 0	6.04	6.2	6.32	V
rising threshold	V <sub>BATT_PRE</sub>	2 cells, REG07h, bits[5:4] = 11, REG30h, bit[3] = 0	6.42	6.6	6.71	V
Pre-charge to fast charge	VBATI_PRE	2 cells, REG07h, bits[5:4] = 01, REG30h, bit[3] = 0	5.85	6.025	6.15	V
falling threshold		2 cells, REG07h, bits[5:4] = 11, REG30h, bit[3] = 0	6.25	6.42	6.54	V
		2 cells, V <sub>BATT</sub> = 5V, REG03h, bits[7:4] = 0010	120	180	240	mA
		2 cells, V <sub>BATT</sub> = 5V, REG03h, bits[7:4] = 0101	170	240	310	mA
Pre-charge current	I <sub>PRE</sub>	2 cells, V <sub>BATT</sub> = 5V, REG03h, bits[7:4] = 1010	400	540	720	mA
		2 cells, V <sub>BATT</sub> = 5V, REG03h, bits[7:4] = 1100	480	660	920	mA
		2 cells, V <sub>BATT</sub> = 5V, REG03h, bits[7:4] = 1111	600	840	1230	mA



 $V_{IN}$  = 5V,  $V_{BATT}$  = 3.7V/cell, RS1 = 10m $\Omega$ ,  $T_A$  = 25°C, unless otherwise noted.

Parameter	Symbol	Condition	Min	Тур	Max	Units
		REG03h, bits[3:0] = 0001	30	145	280	mA
Termination current	I <sub>TERM</sub>	REG03h, bits[3:0] = 0100	280	435	600	mA
		REG03h, bits[3:0] = 1111	1.3	1.5	1.75	Α
Auto-recharge battery voltage threshold	$V_{RECH}$	Below the battery-full voltage, 2 cells, REG04h, bit[0] = 1, REG07h, bits[7:6] = 00	150	210	270	mV /cell
Charge termination deglitch time	t <sub>TERM_DGL</sub>			1.7		sec
Battery over-voltage (OV) threshold	V <sub>BATT_OVP</sub>	2 cells, V <sub>BATT</sub> rising, compare to V <sub>BATT_REG</sub>	140	320	520	mV
Battery OV threshold hysteresis	V BATT_OVP		130	210	290	mV
Virtual diode entry threshold		V <sub>SYS</sub> falling, V <sub>BATT</sub> - V <sub>SYS</sub>		25		mV
Virtual diode quit threshold		V <sub>SYS</sub> rising, V <sub>SYS</sub> - V <sub>BATT</sub>		30		mV
Ideal diode forward voltage in supplement mode	V <sub>FWD</sub>	10mA discharge current		30		mV
V <sub>IN</sub> and Input Current (I <sub>IN</sub> ) Re	gulation					
		REG00h, bits[6:0] = 0001010	410	470	530	mA
I <sub>IN</sub> limit	I <sub>IN_LIM1</sub>	REG00h, bits[6:0] = 0011110	1.4	1.49	1.57	Α
		REG00h, bits[6:0] = 0111100	2.85	3	3.15	Α
		REG01h, bits[7:0] = 00101101	4.28	4.5	4.72	
V <sub>IN</sub> clamp limit threshold	$V_{\text{IN\_MIN}}$	REG01h, bits[7:0] = 01010101	8.25	8.5	8.73	V
		REG01h, bits[7:0] = 10010001	14.1	14.5	14.9	
<b>Battery Temperature Protect</b>	tion (NTC 、	JEITA)				
NTC low-temp rising voltage threshold	Vcold	NTC pin voltage rising as a percentage of V <sub>NTC</sub>	69	71.1	73.5	%
NTC low-temp threshold hysteresis		NTC pin voltage falling		0.9		%
NTC cool-temp rising voltage threshold	Vcool	NTC pin voltage rising as a percentage of V <sub>NTC</sub> , REG0Ah, bits[1:0] = 01	66.5	68.9	71.5	%
NTC cool-temp threshold hysteresis		NTC pin voltage falling		1.3		%
NTC warm-temp falling voltage threshold	Vwarm	NTC pin voltage falling as a percentage of V <sub>NTC</sub> , REG0Ah, bits[3:2] = 01	54	56.1	58.5	%
NTC warm-temp threshold hysteresis		NTC pin voltage rising		1.2		%
NTC hot-temp falling voltage threshold	V <sub>НОТ</sub>	NTC pin voltage falling as a percentage of V <sub>NTC</sub>	46	48.3	50.5	%
NTC hot-temp threshold hysteresis		NTC pin voltage rising		1.4		%

9



 $V_{IN} = 5V$ ,  $V_{BATT} = 3.7V/cell$ , RS1 =  $10m\Omega$ ,  $T_A = 25$ °C, unless otherwise noted.

Parameter	Symbol	Condition	Min	Тур	Max	Units
Thermal Regulation and Prot	ection					
Thermal shutdown rising threshold <sup>(5)</sup>	T	T <sub>J</sub> rising		150		°C
Thermal shutdown hysteresis (5)	T <sub>J_SHDN</sub>	T <sub>J</sub> falling		20		Ŝ
Thermal regulation point (5)	$T_{J_REG}$	Pre-charge stage, REG05h, bits[1:0] = 11		120		ů
Battery-Only Mode						
		V <sub>IN</sub> < V <sub>IN_UVLO</sub> , V <sub>BATT</sub> = 8.4V, BATTFET on, REG0Bh bits[1:0] = 00 to disable PROCHOT and PSYS/ADC functionality		40	60	
Battery leakage current	IBATT_Q	V <sub>IN</sub> < V <sub>IN_UVLO</sub> , V <sub>BATT</sub> = 8.4V, BATTFET on, REG0Bh bits[1:0] = 01 to disable PSYS /ADC but enable PROCHOT functionality			490	μΑ
		V <sub>IN</sub> < V <sub>IN_UVLO</sub> , V <sub>BATT</sub> = 8.4V, BATTFET on, REG0Bh, bits[1:0] = 11 to enable both PSYS/ADC and PROCHOT functionality			2800	
Battery operation UVLO	V <sub>BATT_UVLO</sub>	2 cells, V <sub>BATT</sub> falling		5.2		V
Battery operation UVLO hysteresis		2 cells, V <sub>BATT</sub> rising		560		mV
OTG Operation						
OTG short-circuit entry threshold		V <sub>IN</sub> falling, compare to V <sub>SYS</sub>	40	177	340	mV
OTG short-circuit exit threshold		V <sub>IN</sub> rising, compare to V <sub>SYS</sub>	160	335	520	mV
OTG over-voltage protection (OVP) threshold	Votg_ovp	V <sub>BATT</sub> = 7.4V, V <sub>IN_OTG</sub> rising, as a percentage of the OTG voltage setting, REG0Dh, bits[5:4] = 00		125		%
OTG OVP threshold hysteresis		V <sub>IN_OTG</sub> falling, as a percentage of the OTG voltage setting		7.5		%
OTG output voltage	V <sub>IN_OTG</sub>	I <sub>OTG</sub> = 0A, REG06h, bits[6:0] = 000 0101	4.9	5	5.1	V
OTG output voltage accuracy		As a percentage of V <sub>IN_OTG</sub> , I <sub>OTG</sub> = 0A	-2		+2	%
OTG under-voltage protection (UVP) threshold	Vотg_uv	V <sub>BATT</sub> = 7.4V, V <sub>IN_OTG</sub> falling, as a percentage of the OTG voltage setting, REG0Dh, bits[3:2] = 00		75		%
OTG UVP threshold hysteresis		V <sub>IN_OTG</sub> rising, as a percentage of the OTG voltage setting		7.5		%
OTG output current limit	lolim	REG07h, bits[3:0] = 0110, $V_{BATT} = 7.4V$	1.075	1.43	1.735	Α
OTO output current mint	IOLIM	REG07h, bits[3:0] = 1011, V <sub>BATT</sub> = 7.4V	2.59	2.93	3.27	Α



 $V_{IN} = 5V$ ,  $V_{BATT} = 3.7V/cell$ , RS1 =  $10m\Omega$ ,  $T_A = 25$ °C, unless otherwise noted.

Parameter	Symbol	Condition	Min	Тур	Max	Units
IMVP Requirements			•			
Monitoring Function						
I <sub>IN</sub> indication gain	$V_{IAM}$	$RS1 = 10m\Omega$		250		mV/A
I <sub>IN</sub> indication offset				100		mV
Detter compet in direction rais	$V_{IBM}$	Charging		125		mV/A
Battery current indication gain		Discharging		62.5		mV/A
Battery current indication		Charging		50		mV
offset		Discharging, I <sub>BATT</sub> = 200mA		6.5		mV
System Power Monitor						
System power indicator full scale		256 steps		100		μА
Processor Hot Interruption						
System under-voltage (UV) PROCHOT		REG0Dh, bits[1:0] = 01, V <sub>SYS</sub> falling		5.84		V
System UV PROCHOT hysteresis				160		mV
Battery discharge over- current (OC) PROCHOT		REG0Ch, bits[7:5] = 110, I <sub>BATT</sub> increasing		12		А
Discharge OC PROCHOT deglitch time				25		μs
Input current OC PROCHOT		REG12h, bits[6:3] = 1010, I <sub>IN</sub> increasing		8.2		А
General Comparator		-	1			
General comparator reference		REG0Ch, bit[0] = 0		1.22		V
General comparator hysteresis			40	110	180	mV
General comparator output open-drain MOSFET resistance				200		Ω
<b>Battery Missing Detection</b>						
Battery absent threshold				1.6		V
Battery absent hysteresis				10		mV
Analog-to-Digital Converter (A	ADC) Perfo	rmance				
Sample rate				50		kHz
ADC resolution				10		bits
ADC reference				1.6		V
Logic I/O Pin Characteristics				_		_
Logic low voltage threshold	$V_L$				0.4	V
Logic high voltage threshold	V <sub>H</sub>		1.3			V



 $V_{IN} = 5V$ ,  $V_{BATT} = 3.7V/cell$ , RS1 =  $10m\Omega$ ,  $T_A = 25$ °C, unless otherwise noted.

Parameter	Symbol	Condition	Min	Тур	Max	Units
I <sup>2</sup> C Interface (SDA, SCL)						
Input high threshold level		V <sub>PULL_UP</sub> = 1.8V, SDA and SCL	1.3			V
Input low threshold level		V <sub>PULL_UP</sub> = 1.8V, SDA and SCL			0.4	V
Output low threshold level		Isink = 5mA			0.4	V
I <sup>2</sup> C clock frequency	fscL				400	kHz
Timer Specifications		•				
Digital clock	f <sub>DIG</sub>	VCC LDO enabled	4.5	5	5.5	MHz
Watchdog timer	twdt	REG09h, bits[5:4] = 11		160		sec
Short circuit recovery time				25.6		ms
Trickle charge and pre- charge timer				1		hrs
Total charger timer	t <sub>TMR</sub>	REG09h, bits[2:1] = 10		12		hrs

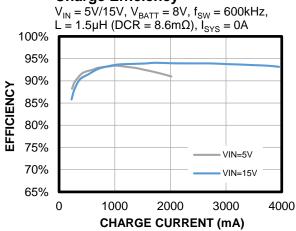
#### Note:

5) Guaranteed by design.

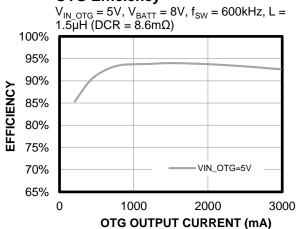


#### TYPICAL CHARACTERISTICS

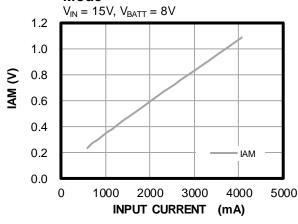
#### **Charge Efficiency**



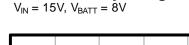
#### **OTG Efficiency**

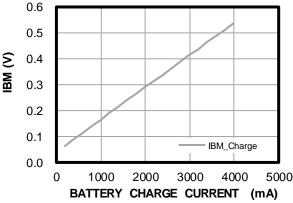


## IAM vs. Input Current in Charge Mode

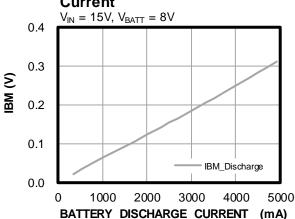


## IBM vs. Battery Charge Current

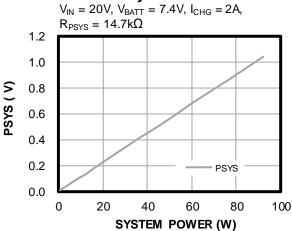




# IBM vs. Battery Discharge Current



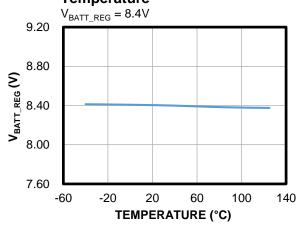
#### **PSYS vs. System Power**



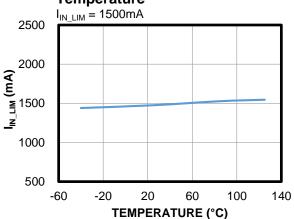


## TYPICAL CHARACTERISTICS (continued)

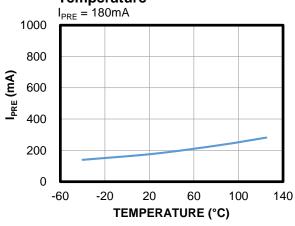
#### **Battery Regulation Voltage vs. Temperature**



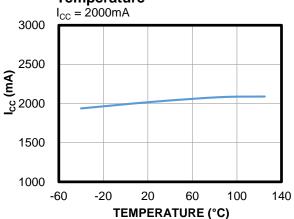
#### Input Current Limit vs. **Temperature**



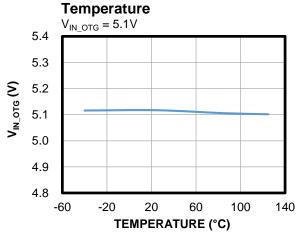
#### Pre-Charge Current vs. **Temperature**



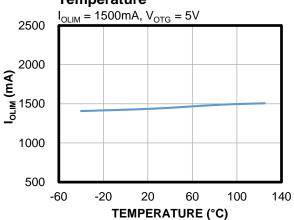
### Fast Charge Current vs. **Temperature**



## OTG Output Voltage vs.



### **OTG Output Current Limit vs. Temperature**

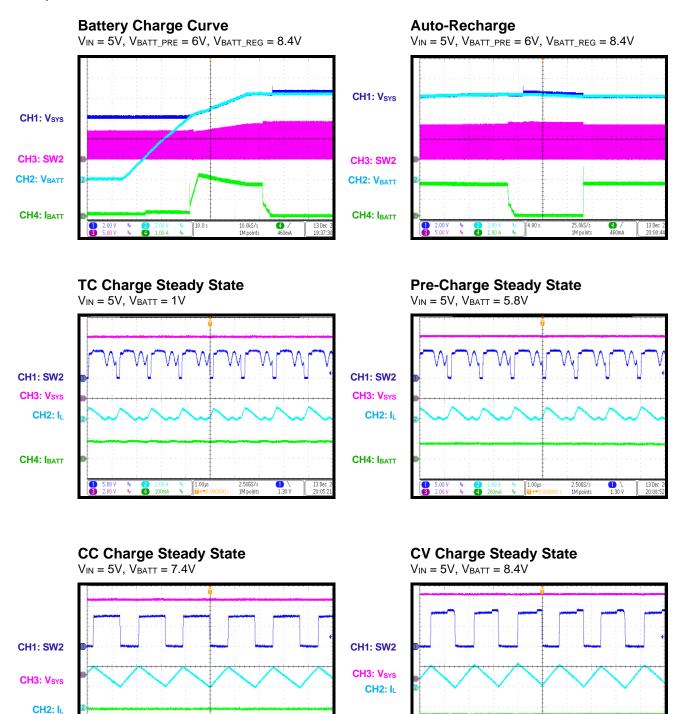




CH4: IBATT

#### TYPICAL PERFORMANCE CHARACTERISTICS

 $V_{IN}=5V,~V_{BATT}=0V$  to 8.4V,  $I_{CC}=2A,~I_{IN\_LIM1}=I_{IN\_LIM2}=3A,~V_{IN\_MIN}=4.5V,~f_{SW}=600kHz,~L=1.5\mu H,~T_A=25^{\circ}C,~unless~otherwise~noted.$ 



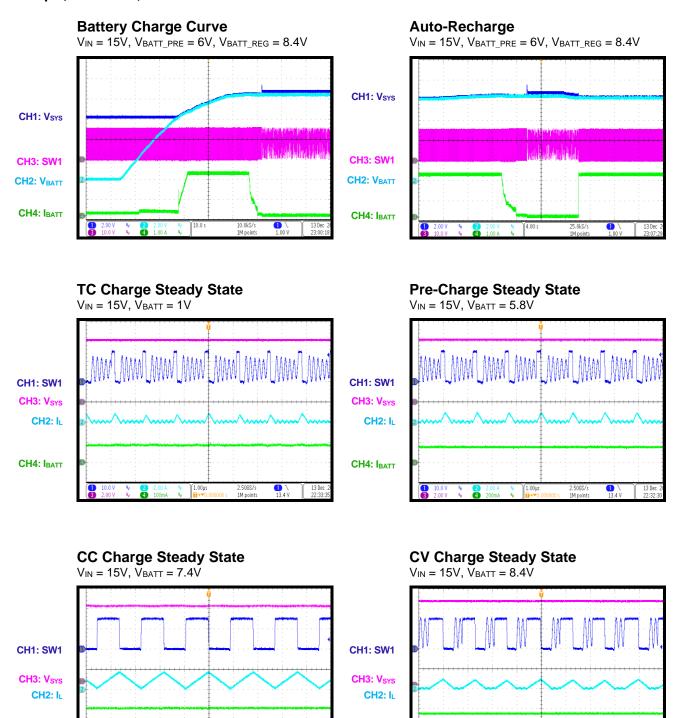
CH4: I<sub>BATT</sub>



СН4: Іватт

## TYPICAL PERFORMANCE CHARACTERISTICS (continued)

 $V_{IN}$  = 15V,  $V_{BATT}$  = 0V to 8.4V,  $I_{CC}$  = 2A,  $I_{IN\_LIM1}$  =  $I_{IN\_LIM2}$  = 3A,  $V_{IN\_MIN}$  = 4.5V,  $f_{SW}$  = 600kHz, L = 1.5 $\mu$ H,  $T_A$  = 25°C, unless otherwise noted.

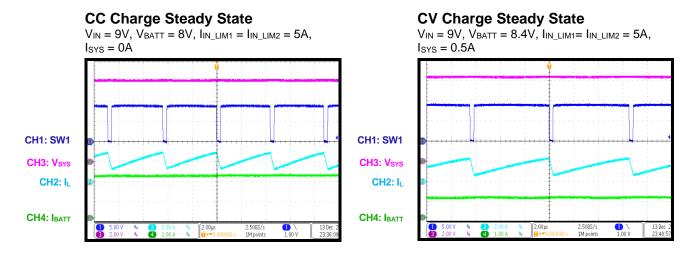


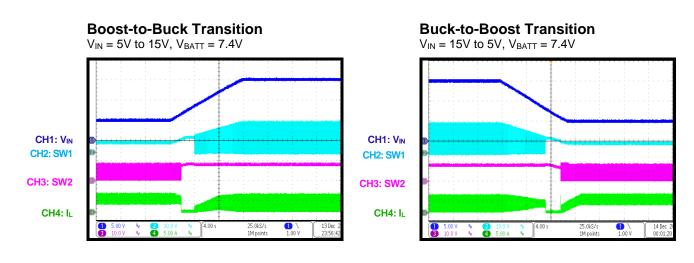
CH4: I<sub>BATT</sub>

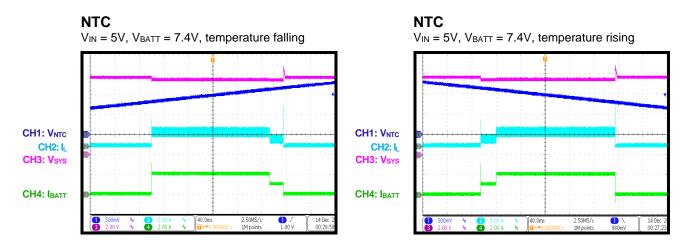


## TYPICAL PERFORMANCE CHARACTERISTICS (continued)

 $V_{BATT}$  = 0V to 8.4V,  $I_{CC}$  = 2A,  $I_{IN\_LIM1}$  =  $I_{IN\_LIM2}$  = 3A,  $V_{IN\_MIN}$  = 4.5V,  $f_{SW}$  = 600kHz, L = 1.5 $\mu$ H,  $T_A$  = 25°C, unless otherwise noted.





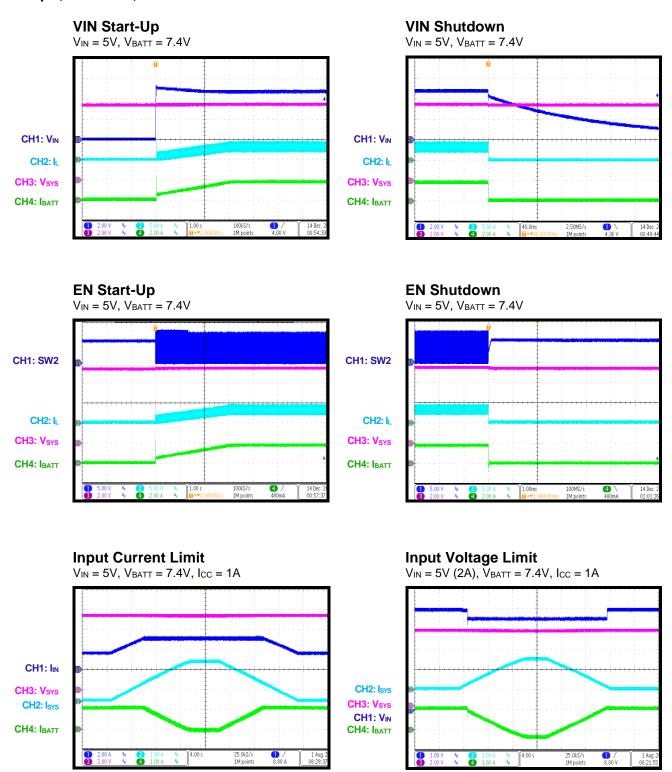


17



## TYPICAL PERFORMANCE CHARACTERISTICS (continued)

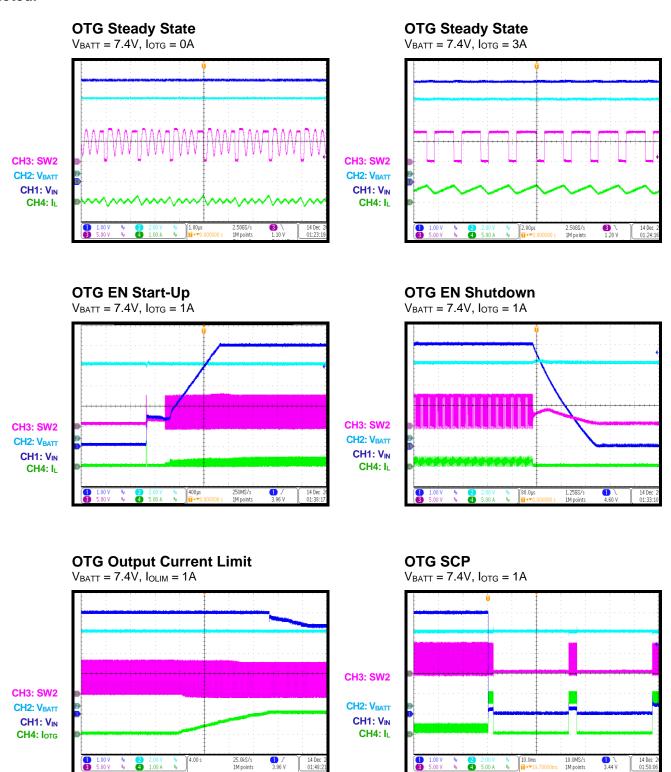
 $V_{IN} = 5V$ ,  $V_{BATT} = 0V$  to 8.4V,  $I_{CC} = 2A$ ,  $I_{IN\_LIM1} = I_{IN\_LIM2} = 3A$ ,  $V_{IN\_MIN} = 4.5V$ ,  $f_{SW} = 600kHz$ , L = 1.5 $\mu$ H, T<sub>A</sub> = 25°C, unless otherwise noted.





## TYPICAL PERFORMANCE CHARACTERISTICS (continued)

 $V_{IN\ OTG}$  = 5V,  $V_{BATT}$  = 0V to 8.4V,  $I_{OLIM}$  = 3A,  $f_{SW}$  = 600kHz, L = 1.5 $\mu$ H,  $T_A$  = 25°C, unless otherwise noted.





### **FUNCTIONAL BLOCK DIAGRAM**

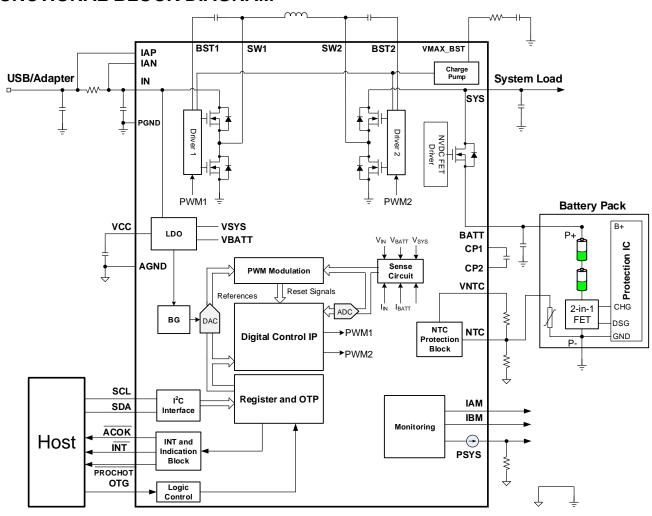


Figure 2: Functional Block Diagram



#### **OPERATION**

The MP2650 is a highly integrated buck or boost charger IC with narrow-voltage DC (NVDC) power path management and USB On-The-Go (OTG) charging for battery packs with 2 cells, 3 cells, or 4 cells in series. All power MOSFETs are integrated to provide a compact system solution size which is easy to use.

The IC can accept a wide input voltage  $(V_{IN})$  range (up to 21V) for charging, and it has two operating modes during the charging process: boost charging mode and buck charging mode, depending on  $V_{IN}$  and the cell count. In buck charging mode, the buck phase (Q1/Q2) switches, while the high-side MOSFET (HSFET) (Q3) of the boost phase is always on (see Figure 3).

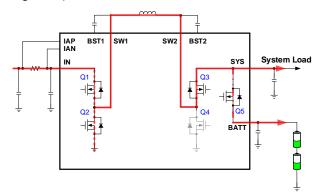


Figure 3: Power MOSFETs' State in Buck
Charging Mode

In boost charge mode, the HS-FET (Q1) of the buck phase is always on, while the boost phase (Q3/Q4) switches (see Figure 4).

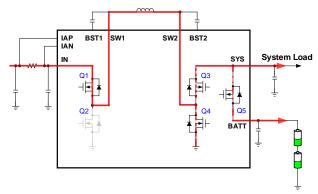


Figure 4: Power MOSFETs' State in Boost Charging Mode

The MP2650 can also provide a constant voltage (5V) at the input in USB OTG mode, and it utilizes a buck converter (Q3/Q4) to provide 5V/3A from the battery pack.

#### **Operation Modes**

The MP2650 offers bidirectional operation modes: charging mode and OTG mode.

When the input is present, the device operates in charging mode. The DC/DC stage in the MP2650 operates as a buck or boost charger depending on  $V_{IN}$  and the cell count. Table 1 lists the DC/DC operation modes.

**Table 1: Operation Modes in Charging** 

Cell Count	Vin	Boost Charge Threshold	Buck Charge Threshold
2	Rising	V <sub>IN</sub> > 6.5V	V <sub>IN</sub> > 8.5V
2	Falling	V <sub>IN</sub> < 5.75V	V <sub>IN</sub> < 8V
3	Rising	$V_{IN} > 6.5V$	$V_{IN} > 15V$
3	Falling	V <sub>IN</sub> < 5.75V	$V_{IN} < 14.5V$
4	Rising	V <sub>IN</sub> > 6.5V	V <sub>IN</sub> > 18V
4	Falling	$V_{IN} < 5.75V$	V <sub>IN</sub> < 17.5V

In charging mode, the MP2650 measures  $V_{\text{IN}}$  to automatically monitor the transition between buck and boost operation. When  $V_{\text{IN}}$  rises from 5V to 20V, the MP2650 charges the battery first in boost mode. Then the device stops switching, unless  $V_{\text{IN}}$  goes high enough for the device to operate in buck mode.

When the input is absent, the MP2650 powers the system from the battery through the integrated battery FET (BATTFET) (Q5). The MP2650 also provides a constant 5V voltage at the input terminal with I<sup>2</sup>C control or hardware pin control, which is USB OTG mode (see Figure 5).

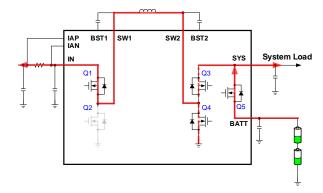


Figure 5: Power FETs' State in OTG Mode

If the IC is not working in charging mode or OTG mode, it enters battery-only mode. Several blocks can be disabled to optimize the battery's quiescent current ( $I_Q$ ). The BATTFET can be turned off to further minimize the battery's  $I_Q$ .

#### **VCC LDO Output**

The VCC LDO supplies the internal bias circuits, as well as the DC/DC converter's drivers. The pull-up rail of the open-drain outputs can also be connected to VCC. VCC has a 3.6V output and a 50mA current capability.

VCC is supplied from either  $V_{\text{IN}}$  or  $V_{\text{SYS}}$ , depending on which has the higher value. When  $V_{\text{IN}}$  or  $V_{\text{SYS}}$  exceed their respective under-voltage lockout (UVLO) thresholds, the sleep comparator, battery depletion comparator, and BATTFET driver are active. In addition, the  $I^2$ C interface is ready for communication, and all registers are reset to their default values. The host can access all the registers.

In charging mode, the internal VCC LDO is enabled when the following conditions are valid:

- V<sub>IN</sub> exceeds its UVLO threshold (V<sub>IN\_UVLO</sub>)
- Thermal shutdown is not occurring

Particularly when  $V_{\text{IN}}$  exceeds  $V_{\text{IN\_UVLO}}$  in 5V boost charge mode, VCC is powered by  $V_{\text{SYS}}$  after charge termination.

When the input is absent, the VCC LDO is powered by the battery.

# Input Under-Voltage Lockout (UVLO) and Input Power-On Reset (POR)

The MP2650 has an input power-on reset (POR) voltage threshold. If  $V_{\text{IN}}$  drops below  $V_{\text{IN\_POR}}$  and the battery is present, only the BATTFET block (charge pump, battery UVLO, battery over-current protection (OCP)) and the I<sup>2</sup>C continue to operate.

The MP2650 also has an input UVLO threshold. If  $V_{\text{IN\_POR}} < V_{\text{IN}} < V_{\text{IN\_UVLO}}$ , then the internal control block reference, digital-to-analog converter (DAC), and analog-to-digital converter (ADC) start to operate. However, the power stage is not ready until  $V_{\text{IN}} > V_{\text{IN\_UVLO}}$ . Then the device can operate in buck or boost charging mode.

#### **Input Power Status Reporting**

The IC qualifies the voltage of the input source before start-up. The input source must meet the following requirements:

V<sub>IN UVLO</sub> < V<sub>IN</sub> < V<sub>IN OVLO</sub>

Once the input power source meets the above conditions, the system status register (REG13h, bit[1]) asserts that the input power is good, and the buck or boost converter is ready to operate.

#### **ACOK Indication**

ACOK is an open-drain output pin indicating the presence of an adapter. It indicates whether the charger is operating normally by pulling ACOK to AGND under the following conditions:

•  $V_{IN} > V_{IN UVLO}$ 

#### **NVDC Power Path Power Management**

The MP2650 is designed as a charger with narrow-voltage DC (NVDC) power path power management, which guarantees the priority of the system power requirement under input plugout or heavy-load conditions (see Figure 6).

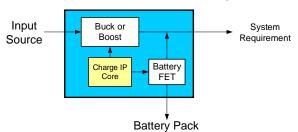


Figure 6: NVDC Power Path Management Structure

The NVDC power path regulates the system voltage  $(V_{SYS})$  within a narrow DC range to provide an optimized system bus voltage for the rails at the system bus. This allows the system to operate even when the battery is completely depleted or removed. When the input source current or voltage limit is reached, power path management automatically reduces the charge current  $(I_{CHG})$  to meet the priority of the system's power requirements. If the system current  $(I_{SYS})$  increases after  $I_{CHG}$  is reduced to 0A, supplement mode allows the battery to power the system along with the input power supply. When the input is absent, the system

is powered by the battery via the integrated BATTFET.

When  $V_{BATT} > V_{BATT\_UVLO}$  and  $V_{IN} < V_{IN\_UVLO}$ , the MP2650 operates in battery-only mode. In this mode, the battery FET fully turns on to power the system using the battery.

When OTG is enabled, the battery supplies power to the input side via the buck converter, as well as the system.

When  $V_{IN\_OVLO} > V_{IN} > V_{IN\_UVLO}$ , the input power supplies the system and charges the battery if charging is enabled. Due to the NVDC structure, when the battery FET is off,  $V_{SYS}$  is regulated above the maximum voltage between  $V_{BATT\_PRE}$  and the battery voltage ( $V_{BATT}$ ) via  $V_{TRACK}$  (see Figure 7). When  $V_{BATT} > V_{BATT\_PRE}$ ,  $V_{SYS}$  tracks  $V_{BATT}$ .

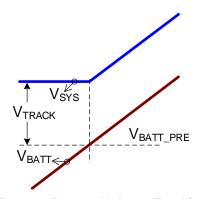


Figure 7: Battery Voltage Tracking

When charging is enabled and no charge fault occurs, BATTFET fully turns on once  $V_{BATT} > V_{BATT\ PRE} + 140 \text{mV}$  (see Figure 8).

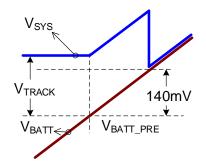


Figure 8: Switching Mode Fast Charging

## Input Voltage Limit and Input Current Limit Regulation

To meet the maximum current limit for the USB specifications and avoid overloading the adapter, the MP2650 features both  $I_{\text{IN}}$  current limiting and  $V_{\text{IN}}$  limiting.

If the preset  $I_{IN}$  limit exceeds the adapter rating, the backup  $V_{IN}$  limit loop works to prevent the input source from being overloaded.

#### IC Thermal Regulation

The IC continuously monitors the internal junction temperature to maximize power delivery and avoid overheating the chip. If the internal junction temperature reaches the preset limit, the IC starts to reduce I<sub>CHG</sub> to prevent higher power dissipation.

#### **Battery Supplement Mode**

When the  $I_{\text{IN}}$  or  $V_{\text{IN}}$  limit loop operates, PWM control limits the power from the input. As a result,  $V_{\text{SYS}}$  and  $I_{\text{CHG}}$  decrease.

If the system power exceeds the input power,  $V_{\text{SYS}}$  keeps falling.  $I_{\text{CHG}}$  drops to 0A or becomes negative, which means the battery must start to discharge and supplement the system. This is called battery supplement mode. In this mode, the system load is powered by the battery and DC/DC converter simultaneously.

#### **Virtual Diode Mode**

In battery supplement mode, a virtual diode mode is designed into the IC to optimize the control transition between BATTFET and DC/DC converter. BATTFET enters virtual diode mode under the following conditions:

- $V_{IN} > V_{IN UVLO}$
- V<sub>SYS</sub> < V<sub>BATT</sub> 25mV

In virtual diode mode, BATTFET operates as an ideal diode with a 30mV forward voltage (from the battery side to system side). When the system voltage is 25mV below the battery voltage, the gate drive of BATTFET is regulated to keep BATTFET's  $V_{DS}$  at about 30mV. As the discharge current increases, BATTFET obtains a stronger gate drive and a smaller  $R_{DS(ON)}$  until BATTFET is fully on. The virtual diode exits when  $V_{SYS}$  exceeds  $V_{BATT}$  by 30mV due to the system's decreasing load current.

#### **USB Suspended Mode**

The IC has a USB suspended mode control bit to turn off the DC/DC converter and force the battery to power the system load, regardless of the  $V_{\text{IN}}$  status.



#### **Charge Cycle**

In charge mode, the IC has six control loops to regulate  $V_{\text{IN}}$ ,  $I_{\text{IN}}$ ,  $V_{\text{SYS}}$ ,  $I_{\text{CHG}}$ , charge voltage, and device junction temperature.

The IC provides four main charging phases: constant current (CC) trickle charge, CC precharge, CC fast charge, and constant voltage (CV) charge. These phases are described below.

#### Constant Current Trickle Charge (Phase 1)

When the input power qualifies as a good power supply, the IC checks  $V_{BATT}$  to determine if trickle current charging is required. If  $V_{BATT}$  is below  $V_{BATT\_TC}$ , a trickle charge current is applied to the battery.

#### Constant Current Pre-Charge (Phase 2)

When  $V_{BATT}$  exceeds  $V_{BATT\_TC}$ , the IC starts to safely pre-charge the deeply depleted battery until  $V_{BATT}$  reaches the pre-charge to fast-charge threshold ( $V_{BATT\_PRE}$ ). If  $V_{BATT\_PRE}$  is not reached before the pre-charge timer (1 hour) expires, then the charge cycle stops and a corresponding timeout fault signal is asserted. The pre-charge current can be configured via the I<sup>2</sup>C (REG03h, bits[7:4]).

#### Constant Current Fast Charge (Phase 3)

If V<sub>BATT</sub> exceeds V<sub>BATT\_PRE</sub> (set by REG07h, bits[5:4]), the IC enters the CC charge (fast charge) phase. The fast charge current can be configured up to 5A via REG02h, bits[6:0].

#### Constant Voltage Charge (Phase 4)

When  $V_{BATT}$  rises to the battery-full voltage  $(V_{BATT\_REG})$  set via REG04h, bits[6:1],  $I_{CHG}$  decreases due to battery voltage loop regulation.

The charge cycle is considered complete when  $I_{\text{CHG}}$  reaches the battery-full termination threshold ( $I_{\text{TERM}}$ ) set via REG03h, bits[3:0], as long as the termination function is enabled. If  $I_{\text{TERM}}$  is not reached before the safety charge timer expires, then the charge cycle stops and the corresponding timeout fault signal is asserted (see the Safety Timer section on page 25).

Note that during the charging process, the actual  $I_{CHG}$  may be below the register setting due to the  $I_{IN}$  loop,  $V_{IN}$  loop, or thermal regulation. The thermal regulation loop reduces  $I_{CHG}$  when the junction temperature exceeds the preset limit. The limit can be configured to be between  $60^{\circ}$ C and  $120^{\circ}$ C. The junction temperature regulation threshold can be set via REG05h, bits[1:0].

A new charge cycle starts once all the following conditions are valid:

- The input power is re-plugged
- Battery charging is enabled by the I<sup>2</sup>C
- No thermistor fault has occurred
- No battery over-voltage (OV) fault has occurred
- BATTFET is not forced to turn off

Re-plugging the input power or toggling the battery charging control bit can restart a charge cycle, even if a fault has not occurred. The new charge cycle can start with any phase, and the phase is determined by  $V_{BATT}$ .

#### **Automatic Recharge**

When charging is terminated, the battery may be discharged because of system consumption or the self-discharge function. When  $V_{BATT}$  is discharged below the configurable recharge threshold, the IC automatically starts a new charging cycle. If the input power is valid, a manual restart is not required. The charging safety timer resets when the auto-recharge cycle begins.

#### **Battery Over-Voltage Protection (OVP)**

The IC provides battery over-voltage protection (OVP). If the battery voltage exceeds the battery OV threshold, charging stops and BATTFET turns off immediately.  $V_{\text{SYS}}$  is regulated at a value above  $V_{\text{BATT}}$  via  $V_{\text{TRACK}}$ .

#### **ADC Conversion and Multiplexer**

The MP2650 integrates a 10-bit SAR ADC with 50ksps. In charge mode, the multiplexer measures  $V_{\text{IN}}$ ,  $I_{\text{IN}}$ ,  $V_{\text{SYS}}$ ,  $V_{\text{BATT}}$ , and  $I_{\text{CHG}}$ . In OTG mode, the multiplexer measures the OTG output voltage, OTG output current, battery voltage, and current.



#### **Safety Timer**

The IC provides both a pre-charge and complete charge safety timer to prevent an extended charging cycle due to abnormal battery conditions. If V<sub>BATT</sub> is below V<sub>BATT\_PRE</sub>, the total safety timer for both trickle charge and pre-charge is 1 hour. The complete charge safety timer includes a trickle charge and pre-charge timer. The user can configure the complete charge safety timer via the I<sup>2</sup>C. Note that the safety timer does not operate in discharge mode.

The safety timer is reset at the beginning of a new charging cycle. It can also be reset by sequentially writing 0 then 1 to REG08h, bit[4]. The following actions restart the safety timer:

- A new charge cycle begins
- Writing REG08h, bit[4] from 0 to 1 (charge enabled)
- Writing REG09h, bit[3] from 0 to 1 (safety timer enabled)

The IC can automatically adjust or suspend the timer if any fault occurs.

The timer is suspended if any of the following conditions occurs:

- The battery supplements the system
- System OVP
- An NTC hot or cold fault

If the  $I_{IN}$  limit,  $V_{IN}$  limit, or thermal regulation limit is reached, the remaining time for the timer can be doubled. Once the condition is removed, the timer returns to its normal value. This function can be enabled or disabled via the  $I^2C$ .

# Impedance Compensation to Accelerate Charging

In the charging cycle, the CV charging stage takes up a significant proportion of the total charging time. To accelerate the charging cycle, it is recommended to remain in the CC charging stage for as long as possible.

The IC allows the user to compensate the intrinsic resistance of the battery by adjusting the charge-full voltage threshold according to  $I_{\text{CHG}}$  and the internal resistance. In addition, a maximum allowed regulated voltage is also set for safety reasons.

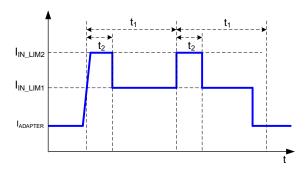
The regulated voltage can be calculated with Equation (1):

$$V_{BATT REG}^* = V_{BATT REG} + Min(I_{CHG} \times R_{BATT CMP}, V_{CLAMP})$$
 (1)

Where  $V_{BATT\_REG}^*$  is the real battery regulation voltage,  $V_{BATT\_REG}$  is the charge-full voltage set via REG04h, bits[6:1],  $I_{CHG}$  is the real-time charge current, and Min means the smaller value between ( $I_{CHG} \times R_{BATT\_CAMP}$ ) and ( $V_{CLAMP}$ ) should be used for the calculation.

#### **Two-Level Input Current Limit**

The  $I_{IN}$  limit has two thresholds:  $I_{IN\_LIM1}$  for the lower limit, and  $I_{IN\_LIM2}$  for the higher limit.  $I_{IN\_LIM2}$  can only last for  $t_2$ , and repeat once in  $t_1$ . Figure 9 shows the two current limit levels, as well as the time durations for  $t_2$  and  $t_1$ .



**Figure 9: Two-Level Current Limit** 

The two-level current limit function is initiated when  $I_{IN}$  is close to 100mA and below  $I_{IN\_LIM1}$ . It starts at  $I_{IN\_LIM2}$  for  $t_2$ , and then changes to  $I_{IN\_LIM1}$  for  $t_1$  before repeating the pattern. This fully utilizes the input adapter surge capability to extend the battery life.

 $I_{\text{IN\_LMT1}}$  and  $I_{\text{IN\_LMT2}}$  can be configured through  $I^2C$  registers REG00h and REG0Fh, respectively.  $t_2$  and  $t_1$  can be configured through  $I^2C$  registers REG10h and REG11h, respectively.

# System Power Monitor Analog Output (PSYS)

The IC has a PSYS pin to monitor the real-time system power in charging mode. The PSYS pin provides a current signal proportional to the total power consumed by the platform. Estimate the total system power (Psys) with Equation (2):

$$P_{SYS} = K_{PSYS} x \left( V_{IN} x I_{IN} + V_{BATT} x I_{BATT} \right) (2)$$

Where  $V_{IN}$  is the adapter voltage,  $I_{IN}$  is the adapter current,  $V_{BATT}$  is the battery voltage, and  $I_{BATT}$  is the battery discharging current. When the battery is charged,  $I_{BATT}$  is a negative value.

PSYS is an analog-controlled current source output that is proportional to the system power, and has a 0.78µA/W gain. The MP2650 also has a 10-bit register that reports the system power, with a resolution of 0.125W/bits. The PSYS function can be enabled or disabled through REG0Bh, bits[1:0].

#### **Current Monitoring (IAM/IBM)**

The IC has an IBM pin to obtain the real-time battery current ( $I_{BATT}$ ) in both charge mode and discharge mode. The IBM voltage ( $V_{IBM}$ ) is a fraction of the charge current. It indicates the amount of charge current flowing into and out of the battery during charge and discharge mode, respectively.  $V_{IBM}$  can be estimated with Equation (3):

$$V_{IBM} = I_{BATT} \times 0.125(V)$$
 (3)

The IBM pin can report the charge current or discharge current depending on the  $I^2C$  register setting. Similarly, the MP2650 also monitors  $I_{IN}$  during the charging and discharging processes using the IAM pin. The IAM voltage ( $V_{IAM}$ ) can be calculated with Equation (4):

$$V_{IAM} = I_{IN} \times 0.25(V)$$
 (4)

The MP2650 also has registers to store  $I_{\rm IN}$  (REG1E~1Fh), OTG current (REG22~23h),  $I_{\rm CHG}$  (REG1A~1Bh), and discharge current (REG28~29h). When the battery is charged in charge mode, the results in the OTG current and discharge current registers are set to 0. In OTG mode or battery supplement mode, the results in the input current and charge current registers are set to 0.

#### **Processor Hot Interrupt (PROCHOT)**

The IC continuously monitors I<sub>IN</sub>, V<sub>SYS</sub>, the battery discharge current, input source presence, and whether the battery is present.

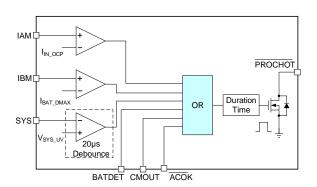
The PROCHOT pin is pulled low if any of the following conditions occur:

- I<sub>IN</sub> > I<sub>IN</sub> OCP
- $I_{BATT} > I_{BAT\_DMAX}$

- V<sub>SYS</sub> < V<sub>SYS</sub> UV
- Adapter plug-out
- Battery plug-out
- An independent comparator has asserted

The thresholds for  $I_{IN\_OCP}$ ,  $I_{BAT\_DMAX}$ , and  $V_{SYS\_UV}$  are configurable via the  $I^2C$ . To set the PROCHOT assertion threshold for adapter over-current (OC) conditions, write an  $I_{IN\_OCP}$  command to REG12h. If the adapter current exceeds the  $I_{IN\_OCP}$  threshold, the PROCHOT signal asserts after the debounce time. The signal latches on for a minimum time, which is configured via REG0Eh (see Figure 10).

 $V_{SYS\_UV}$  has two optional debouncing times (10µs or 20µs), which can be set via REG0Ch, bit[4]. Other triggering events have the same debouncing time, which can also be set via REG0Eh.



**Figure 10: PROCHOT Events** 

#### **Battery-Only Mode**

If the input is absent, OTG mode is disabled, and  $V_{BATT}$  exceeds  $V_{BATT\_UVLO}$ , then BATTFET fully turns on. The  $10m\Omega$  BATTFET minimizes the conduction loss. The IC's  $I_Q$  is as low as  $30\mu A$ .

The low on resistance and low  $I_{\mathbb{Q}}$  help to extend the battery's runtime.

#### **Light-Load Operation**

Under light loads in buck mode, one of the phases can be disabled manually or automatically via the I<sup>2</sup>C. Light-load operation is designed to optimize the switching frequency (f<sub>SW</sub>).



When the system current decreases,  $V_{SYS}$  rises and  $t_{ON}$  shortens. Then  $t_{OFF}$  is extended to keep the frequency constant. Finally,  $t_{OFF}$  reaches its limit and  $t_{ON}$  reaches the minimum on time. If  $V_{SYS}$  still increases, the on time is skipped once  $V_{SYS}$  exceeds 102% of  $V_{SYS\_REG}$ . The threshold can be adjusted via REG31h, bits[1:0].

#### **USB On-The-Go (OTG) Mode**

In discharge mode, the regulated 5V/3A power is delivered from the battery to the IN pin through a single-phase buck converter.

The IC does not enter OTG mode if the battery is below the configurable battery UVLO threshold. This ensures that the battery is not drained. To enable buck mode, the input voltage at the IN pin must be below 1V.

OTG operation can be enabled when REG08h, bit[5] = 1, and the OTG pin is high. The USB OTG output current can be set between 0A and 3.75A via the I<sup>2</sup>C (REG07h, bits[3:0]). Buck mode is enabled when all of the following conditions are met:

- VBATT > VBATT UVLO
- OTG REG08h, bit[5] = 1
- A 30ms delay has completed
- The OTG pin is high
- V<sub>IN</sub> < 1V</li>

If  $V_{\text{IN}}$  does not exceed  $V_{\text{OTG\_UV}}$  (set by REG0Dh, bits[3:2]) within 30ms while OTG is enabled, a buck fault asserts, and buck mode is disabled until a command that enables OTG operation is reissued.

The IC also features output short-circuit protection (SCP) and output OVP. If the load current approaches the OTG current-limit threshold (set via the I²C) while the IC runs in buck mode, the OTG output current loop dominates, and the converter acts as a current source. If  $V_{\text{BUS}}$  falls below  $V_{\text{OTG\_UV}}$  for more than 700µs, a buck fault is asserted. The buck is disabled and restarts after a 30ms delay time. Any fault during OTG buck operation sets the fault register (REG14h, bit[6]) to 1.

When both charging and OTG buck mode are enabled, OTG buck mode takes priority.

The IC continuously monitors the voltage at the IN pin in OTG buck mode. If V<sub>BUS</sub> exceeds V<sub>OTG OV</sub> (set via REG0Dh, bits[5:4]), then the IC

stops switching and the corresponding fault register is set high to indicate the fault.

#### **Thermal Shutdown Protection**

Thermal shutdown protection is also active in OTG mode. If the junction temperature exceeds 150°C, the MP2650 enters thermal shutdown. Once the junction temperature drops below 120°C, the device resumes normal operation.

#### **Host Mode and Default Mode**

The IC is a host-controlled device. After POR, the IC starts in the watchdog timer expiration state, or its default mode. All registers revert to their default settings.

Any write to the IC is transmitted to host mode. All of the device parameters can be configured by the host. To keep the device in host mode, the host must reset the watchdog timer regularly by writing 1 to REG08h, bit[6] before the watchdog timer expires. The IC goes back to default mode once the watchdog timer expires.

The MP2650 has a one-time programmable (OTP) memory to program the default value of certain registers after they are assembled.

#### I<sup>2</sup>C Interface

The IC uses an I<sup>2</sup>C-compatible interface that sets flexible charging parameters and reports device statuses instantaneously. The I<sup>2</sup>C is a bidirectional, two-wire serial interface. Only two bus lines are required: a serial data line (SDA) and a serial clock line (SCL). The device can be considered a master or a slave when performing data transfers. The master is the device that initiates a data transfer on the bus and generates the clock signals to permit the transfer. Any device addressed by the master is considered a slave.

The device operates as a slave device with address 5Ch, and receives control inputs from the master device, such as a microcontroller (MCU) or digital signal processor.

The I<sup>2</sup>C interface supports both standard mode (up to 100kbits), and fast mode (up to 400kbits). Both SDA and SCL are connected to the positive supply voltage via a current source or pull-up resistor.



When the bus is free, both lines are high. The SDA and SCL pins are open drains.

The data on SDA must be stable during the high period of the clock. The high or low state of

the data line can only change when the clock signal on SCL is low. One clock pulse is generated for each data bit transferred (see Figure 11).

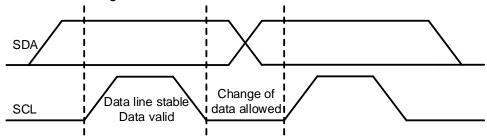


Figure 11: Bit Transfer on the I2C Bus

All the transactions begin with a start condition (S) and are terminated by a stop condition (P). A high-to-low transition on SDA while SCL is high defines a start condition. A low-to-high transition on SDA when SCL is high defines a

stop condition. Start and stop conditions are always generated by the master. The bus is considered busy after the start condition, and is free after the stop condition (see Figure 12).

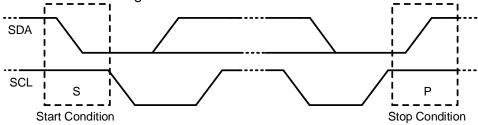


Figure 12: Start and Stop Conditions

Every byte on SDA must be 8 bits long. The number of bytes to be transmitted per transfer is unrestricted. Each byte must be followed by

an acknowledge (ACK) bit. Data is transferred with the most significant bit (MSB) first (see Figure 13).

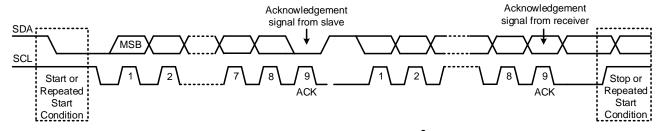


Figure 13: Data Transfer on the I<sup>2</sup>C Bus

The acknowledgement takes place after every byte. ACK bit allows the receiver to signal to the transmitter that the byte was successfully received and that another byte may be sent. All clock pulses, including the 9th (ACK) clock pulse, are generated by the master.

The transmitter releases SDA during the ACK clock pulse, so the receiver can pull SDA low. If SDA remains high during the 9th clock pulse, this is called a not acknowledge (NACK) signal. The master can then generate either a stop condition to abort the transfer, or a repeated start condition to start a new transfer.



After the process is initiated, a slave address is sent. This address is 7 bits long, followed by an 8th data direction bit (R/W). A 0 indicates a

transmission (write), and a 1 indicates a request for data (read). Figure 14 shows the complete data transfer.

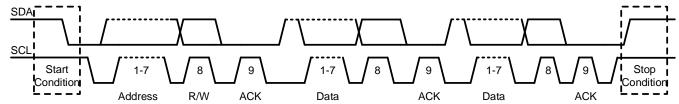


Figure 14: Complete Data Transfer

If the register address is not defined, then the charger IC sends back NACK and reverts to its idle state.

Figure 15, Figure 16, Figure 17, and Figure 18 show examples of I<sup>2</sup>C processes.

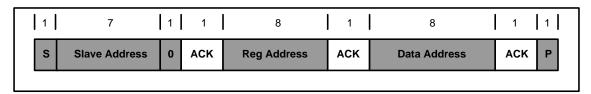


Figure 15: I<sup>2</sup>C Single Write



Figure 16: I<sup>2</sup>C Single Read

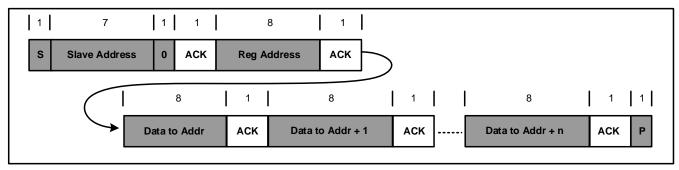


Figure 17: I<sup>2</sup>C Multi-Write

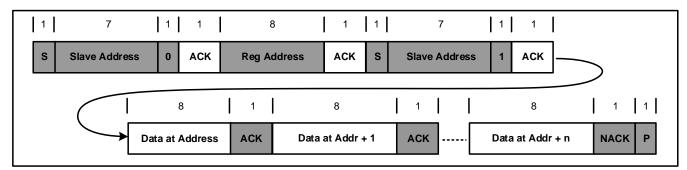


Figure 18: I<sup>2</sup>C Multi-Read





## **REGISTER MAP (Device Address: 5Ch)**

Register Name	Register Address	OTP?	R/W	Description		
REG00h	0x00	Yes	R/W	Input current limit 1 setting		
REG01h	0x01	Yes	R/W	Input voltage limit setting		
REG02h	0x02	Yes	R/W	Charge current setting		
REG03h	0x03	Yes	R/W	Pre-charge and termination current setting		
REG04h	0x04	Yes	R/W	Battery-full voltage and recharge threshold setting		
REG05h	0x05	No	R/W	Battery impedance compensation and junction temperaturegulation		
REG06h	0x06	Yes	R/W	OTG voltage setting		
REG07h	0x07	Yes	R/W	Pre-charge threshold and OTG output current limit setting		
REG08h	0x08	Yes	R/W	Configuration register 0		
REG09h	0x09	Yes	R/W	Configuration register 1		
REG0Ah	0x0A	No	R/W	Configuration register 2		
REG0Bh	0x0B	Yes	R/W	Configuration register 3		
REG0Ch	0x0C	Yes	R/W	Configuration register 4		
REG0Dh	0x0D	Yes	R/W	System/OTG under-voltage and over-voltage setting		
REG0Eh	0x0E	Yes	R/W	PROCHOT interrupt debounce time and duration time setting		
REG0Fh	0x0F	Yes	R/W	Input current limit 2 setting		
REG10h	0x10	Yes	R/W	Input current limit 2 duration setting		
REG11h	0x11	Yes	R/W	Two-level input current limit period setting		
REG12h	0x12	Yes	R/W	Input OCP threshold for triggering PROCHOT		
REG13h	0x13	No	R	Status register		
REG14h	0x14	No	R	Fault register		
REG16~17h	0x16	No	R	ADC result for the battery voltage		
REG18~19h	0x18	No	R	ADC result for the system voltage		
REG1A~1Bh	0x1A	No	R	ADC result for the battery charge current		
REG1C~1Dh	0x1C	No	R	ADC result for the input voltage		
REG1E~1Fh	0x1E	No	R	ADC result for the input current		
REG20~21h	0x20	No	R	ADC result for the OTG output voltage		
REG22~23h	0x22	No	R	ADC result for the OTG output current		
REG24~25h	0x24	No	R	ADC result for the junction temperature		
REG26~27h	0x26	No	R	ADC result for the system power		
REG28~29h	0x28	No	R	ADC result for the battery discharge current		
REG2Bh	0x2B	Yes	R/W	Battery OVP deglitch time		
REG2Dh	0x2D	Yes	R/W	Battery voltage loop enable		
REG30h	0x30	Yes	R/W	Battery pre-charge threshold option		
REG31h	0x31	Yes	R/W	System voltage threshold for pulse skipping		
REG33h	0x33	Yes	R/W	INT mask for Hi-Z mode entry and exit		
REG36h	0x36	Yes	R/W	Analog frequency loop enable		
REG40~41h	0x40	No	R	ADC result for NTC voltage		
REG48h	0x48	No	R	Hi-Z mode indication		





## **REG00h: Input Current Limit 1 Setting**

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
7	RESERVED	0	N/A	N/A	N/A	Reserved.	Reserved.
6	I <sub>IN_LIM1</sub> [6]	0	Υ	Υ	R/W	3200mA.	
5	I <sub>IN_LIM1</sub> [5]	0	Υ	Υ	R/W	1600mA.	
4	I <sub>IN_LIM1</sub> [4]	1	Υ	Υ	R/W	800mA.	Default: 1.5A Range: 0mA to 5A
3	I <sub>IN_LIM1</sub> [3]	1	Y	Y	R/W	400mA.	Offset: 0mA  These bits set the I <sub>IN</sub> limit setting
2	I <sub>IN_LIM1</sub> [2]	1	Y	Υ	R/W	200mA.	(RS = 10m $\Omega$ ). These bits can be configured via the OTP.
1	I <sub>IN_LIM1</sub> [1]	1	Y	Υ	R/W	100mA.	-
0	I <sub>IN_LIM1</sub> [0]	0	Y	Υ	R/W	50mA.	

## **REG01h: Input Voltage Limit Setting**

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
7	VIN_MIN[7]	0	Y	Υ	R/W	12800mV.	
6	VIN_MIN[6]	0	Y	Υ	R/W	6400mV.	
5	VIN_MIN[5]	1	Y	Υ	R/W	3200mV.	Default: 4.5V
4	VIN_MIN[4]	0	Υ	Y	R/W	1600mV.	Range: 0V to 25.5V
3	V <sub>IN_MIN</sub> [3]	1	Y	Υ	R/W	800mV.	These bits set the V <sub>IN</sub> limit threshold. These bits can be
2	VIN_MIN[2]	1	Y	Y	R/W	400mV.	configured via the OTP.
1	VIN_MIN[1]	0	Y	Υ	R/W	200mV.	
0	VIN_MIN[0]	1	Y	Y	R/W	100mV.	



## **REG02h: Charge Current Setting**

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
7	RESERVED	0	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
6	Icc[6]	0	Y	Y	R/W	3200mA.	
5	Icc[5]	0	Υ	Y	R/W	1600mA.	
4	Icc[4]	1	Y	Y	R/W	800mA.	Default: 1A Range: 0A to 5A
3	Icc[3]	0	Y	Y	R/W	400mA.	Offset: 0A
2	Icc[2]	1	Y	Y	R/W	200mA.	These bits set I <sub>CHG</sub> . These bits can be configured via the OTP.
1	Icc[1]	0	Y	Υ	R/W	100mA.	
0	Icc[0]	0	Y	Y	R/W	50mA.	

## **REG03h: Pre-Charge and Termination Current Setting**

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
7	IPRE[3]	0	Y	Y	R/W	0000: 180mA 0001: 180mA 0010: 180mA 0011: 180mA	
6	I <sub>PRE</sub> [2]	0	Y	Y	R/W	0100: 180mA 0101: 240mA 0110: 300mA 0111: 360mA	Default: 180mA Offset: 0mA
5	I <sub>PRE</sub> [1]	1	Y	Y	R/W	1000: 420mA 1001: 480mA 1010: 540mA 1011: 600mA	These bits set the pre-charge current limit. These bits can be configured via the OTP.
4	I <sub>PRE</sub> [0]	1	Y	Y	R/W	1100: 660mA 1101: 720mA 1110: 780mA 1111: 840mA	
3	I <sub>TERM</sub> [3]	0	Y	Y	R/W	800mA.	Default: 200mA
2	I <sub>TERM</sub> [2]	0	Y	Y	R/W	400mA.	Range: 0mA to 1500mA Offset: 0mA
1	I <sub>TERM</sub> [1]	1	Y	Y	R/W	200mA.	These bits set the termination current limit. These bits can be
0	I <sub>TERM</sub> [0]	0	Y	Y	R/W	100mA.	configured via the OTP.



## REG04h: Battery-Full Voltage and Recharge Threshold Setting

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
7	RESERVED	0	N/A	N/A	NA	Reserved.	Reserved.
6	VBATT_REG[5]	1	Υ	Y	R/W	400mV/cell.	
5	VBATT_REG[4]	0	Υ	Y	R/W	200mV/cell.	Default: 4.2V/cell Range: 3.7125V/cell to
4	VBATT_REG[3]	0	Υ	Y	R/W	100mV/cell.	4.5V/cell Offset: 3.7125V/cell
3	VBATT_REG[2]	1	Υ	Y	R/W	50mV/cell.	These bits set the charge-full
2	V <sub>BATT_REG</sub> [1]	1	Υ	Y	R/W	25mV/cell.	voltage. These bits can be configured via the OTP.
1	V <sub>BATT_REG</sub> [0]	1	Υ	Y	R/W	12.5mV/cell.	
0	Vrech_os	0	Y	Y	R/W	0: 100mV/cell 1: 200mV/cell	Offset: 100mV/cell  This bit sets the battery recharge threshold offset. This bit can be configured via the OTP.

## **REG05h: Battery Impedance Compensation and Junction Temperature Regulation**

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment	
7	R <sub>BATT</sub> [2]	0	Y	Y	R/W	100mΩ.	Default: 0mΩ Range: 0mΩ to 175mΩ	
6	R <sub>BATT</sub> [1]	0	Y	Υ	R/W	50mΩ.	These bits set the IR	
5	R <sub>BATT</sub> [0]	0	Y	Y	R/W	25mΩ.	compensation resistor for each cell. These bits can be configured via the OTP.	
4	Vclamp[2]	0	Y	Y	R/W	120mV.	Default: 0mV Range: 0mV to 210mV Offset: 0mV	
3	V <sub>CLAMP</sub> [1]	0	Y	Y	R/W	60mV.	These bits set the IR compensation resistor clamp for each cell (above the	
2	VCLAMP[0]	0	Y	Y	R/W	30mV.	charge voltage limit). These bits can be configured via the OTP.	
1	T <sub>REG</sub> [1]	1	Y	Y	R/W	00: 60°C 01: 80°C	Default: 11 These bits set the thermal	
0	T <sub>REG</sub> [0]	1	Y	Y	R/W	10: 100°C 11: 120°C	regulation threshold. This is only for the BATTFET linear charge loop.	



## **REG06h: OTG Voltage Setting**

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment	
7	RESERVED	0	N/A	N/A	N/A	Reserved.	Reserved.	
6	VIN_OTG[2]	0	Y	Y	R/W		Default: 000	
5	V <sub>IN_OTG</sub> [1]	0	Y	Y	R/W	000: 4.75\/	These bits set the OTG	
4	V <sub>IN_OTG</sub> [0]	0	Y	Y	R/W	000: 4.75V	voltage. These bits can be configured via the OTP.	
3	V <sub>IN_OTG_OS</sub> [3]	0	Υ	Y	R/W	400mV.	Default: 250mV	
2	V <sub>IN_OTG_OS</sub> [2]	1	Y	Y	R/W	200mV.	These bits set the	
1	VIN_OTG_OS[1]	0	Y	Y	R/W	100mV.	secondary OTG voltage. These bits can be	
0	VIN_OTG_OS[0]	1	Y	Y	R/W	50mV.	configured via the OTP.	

## REG07h: Pre-Charge Threshold and OTG Output Current Limit Setting

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
7	BAT_NUM[1]	0	Υ	Y	R/W	00: 2 cells	Default: 00 These bits set the
6	BAT_NUM[0]	0	Y	Y	R/W	01: 3 cells 10/11: 4 cells	battery cell count in series. These bits can be configured via the OTP.
5	Vbatt_pre[1]	0	Y	Y	R/W	Option 1: 00: 2.9V/cell 01: 3V/cell 10: 3.1V/cell 11: 3.2V/cell	Default: 3V/cell  These bits set the battery pre-charge
4	VBATT_PRE[0]	1	Υ	Y	R/W	Option 2: 00: 3.3V/cell 01: 3.4V/cell 10: 3.7V/cell 11: 3.6V/cell	threshold. These bits can be configured via the OTP. The option is set by REG30h, bit[3].
3	Іотд[3]	0	Y	Υ	R/W	2000mA.	Default: 1A
2	l <sub>от</sub> [2]	1	Y	Y	R/W	1000mA.	Range: 0mA to 3.75A Offset: 0mA
1	I <sub>ОТG</sub> [1]	0	Y	Υ	R/W	500mA.	These bits set the OTG current limit. These bits
0	I <sub>OTG</sub> [0]	0	Y	Y	R/W	250mA.	can be configured via the OTP.



## **REG08h: Configuration Register 0**

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
7	REG_RST	0	Y	Y	R/W	Keep the current register setting     Reset to the default register value and reset the safety timer	Default: 0  This bit sets the register reset. It resets to 0 after the register is reset.
6	WTD_RST	0	Y	Y	R/W	0: Normal 1: Reset	Default: 0  This bit sets the I <sup>2</sup> C watchdog timer reset. It resets to 0 after the register is reset.
5	OTG_EN	0	Y	Y	R/W	0: Disable OTG 1: Enable OTG	Default: 0  This bit configures the OTG mode configuration. OTG_EN overrides the charge enable function.
4	CHG_EN	1	Y	Y	R/W	0: Charge disabled (only turn off BATTFET) 1: Charge enabled	Default: 1  This bit configures the charge mode. OTG_EN overrides the CHG_EN enable function. This bit can be configured via the OTP.
3	SUSP_EN	0	Y	Y	R/W	0: Disable SUSP mode 1: Enable SUSP mode (only turn off the DC/DC stage)	Default: 0 This bit configures suspend mode.
2	NTC_ GCOMP_ SEL	1	Y	Y	R/W	0: The OTG/CMIN pin acts as CMIN, the VNTC/CMOUT pin acts as CMOUT, and the NTC/BATDET pin acts as BATDET 1: The OTG/CMIN pin acts as OTG, the VNTC/CMOUT pin acts as VNTC, and the NTC/BATDET pin acts as NTC	Default: 1  This bit selects the NTC and OTG pin functions. When the OTG pin is selected as the independent comparator input, the internal OTG pin is pulled high for OTG mode. This bit can be configured via the OTP.
1	BATTFET_EN	1	Y	Y	R/W	0: Disable charging or discharge 1: Enable charging or discharge	Default: 1 This bit configures the BATTFET.
0	RESERVED	0	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.





## **REG09h: Configuration Register 1**

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
7	RESERVED	0	N/A	N/A	N/A	Reserved.	Reserved.
6	EN_TERM	1	Y	Y	R/W	0: Disabled 1: Enabled	Default: 1 This bit enables charging termination.
5	WTD[1]	0	Y	Y	R/W	00: Disable the timer 01: 40s 10: 80s 11: 160s	Default: 00  This bit sets the I <sup>2</sup> C watchdog timer. These bits can be configured via the OTP.
4	WTD[0]	0	Υ	Y	R/W		
3	EN_TMR	1	Y	Y	R/W	0: Disabled 1: Enabled	Default: 1  This bit enables the charging safety timer (both the pre-charge timer and complete charge cycle timer). This bit can be configured via the OTP.
2	CHG_TMR [1]	1	Y	Y	R/W	00: 5 hours 01: 8 hours 10: 12 hours 11: 20 hours	Default: 10  This bit sets the fast-charge timer. These bits can be configured via the OTP.
1	CHG_TMR [0]	0	Y	Υ	R/W		
0	TMR2X_EN	0	Y	Y	R/W	O: The safety timer is not doubled during input DPM or thermal regulation  1: The safety timer is doubled during input DPM and thermal regulation	Default: 0 This bit sets the safety timer during input DPM and thermal regulation.





# **REG0Ah: Configuration Register 2**

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
7	JEITA_ISET	0	Y	Y	R/W	0: 50% 1: 20%	Default: 0 This bit sets the JEITA low-temperature current. It is a percentage of the value set by REG02h, bits[6:0]. This bit is only valid when REG0Ah, bits[5:4] = 00.
6	JEITA_ VSET	0	Y	Y	R/W	0: Set the charge voltage to VBATT_REG - 75mV x cell count 1: Set the charge voltage to VBATT_REG - 150mV x cell count	Default: 0  This bit sets the JEITA high-temperature voltage. It is only valid when REGOAh, bits[5:4] = 00.
5	NTC_CTRL [1]	1	Y	Υ	R/W	00: JEITA	Default: 11
4	NTC_CTRL [0]	1	Y	Y	R/W	01/10: Standard 11: Disabled	These bits set the NTC protection type.
3	NTC_WARM [1]	0	Y	Y	R/W	00: 58.3% (40°C)	Default: 01
2	NTC_WARM [0]	1	Y	Y	R/W	01: 56.1% (45°C) 10: 53.7% (50°C) 11: 51.3% (55°C)	These bits set the NTC warm temperature threshold (a percentage of VNTC).
1	NTC_COOL [1]	1	Y	Y	R/W	00: 70.7% (0°C)	Default: 10
0	NTC_COOL [0]	0	Y	Y	R/W	01: 69.7% (5°C) 10: 68.6% (10°C) 11: 67.3% (15°C)	These bits set the NTC cool temperature threshold (a percentage of VNTC).





## **REG0Bh: Configuration Register 3**

			1	1		1	
Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
7	RESERVED	0	N/A	N/A	N/A	Reserved.	Reserved.
6	RESERVED	0	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
5	IBM_CFG	0	N	N	R/W	Reflect the battery discharge current     Reflect the battery charge current	Default: 0 This bit configures the battery current monitor.
4	SW_FREQ[1]	0	Y	Y	R/W	00: 600kHz 01: 800kHz	Default: 00  These bits set f <sub>sw</sub> .
3	SW_FREQ[0]	0	Y	Y	R/W	10: 1000kHz 11: 1250kHz	These bits can be configured via the OTP.
2	RESERVED	0	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
1	PROCHOT/ PSYS_CFG[1]	0	Y	Y	R/W	00: Disable PROCHOT and PSYS functionality (lowest Io) 01: Enable PROCHOT	Default: 00  These bits set the function setting in
0	PROCHOT/ PSYS_CFG[0]	0	Y	Y	R/W	and disable PSYS (middle IQ, since part of the circuit is enabled) 10/11: Enable PROTHOT and PSYS	battery-only mode. These bits can be configured via the OTP.





# **REG0Ch: Configuration Register 4**

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
7	DSCHG_OC_ PROCHOT[2]	1	Υ	Y	R/W	000: 0A 001: 2A	Default: 110
6	DSCHG_OC_ PROCHOT[1]	1	Y	Y	R/W	010: 4A 011: 6A 100: 8A	These bits set the battery discharge over-current (OC) threshold for PROCHOT
5	DSCHG_OC_ PROCHOT[0]	0	Υ	Y	R/W	101: 10A 110: 12A 111: 14A	assertion. These bits can be configured via the OTP.
4	VSYS_ PROCHOT_ TDB	0	Y	Y	R/W	0: 10μs 1: 20μs	Default: 0 This bit sets the VSYS undervoltage (UV) trigger PROCHOT debounce time. This bit is set via the OTP.
3	VIRTUAL_ DIODE_EN	0	Y	Y	R/W	0: Disabled 1: Enabled	Default: 0  This bit sets the ideal diode mode when an adapter is absent. This bit can be configured via the OTP.
2	RESERVED	0	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
1	INDEPENDENT_ COMPARATOR_ CFG	0	Y	Y	R/W	0: PROCHOT does not assert 1: PROCHOT asserts	Default: 0  This bit sets the PROCHOT assertion when the independent comparator outputs low. This bit can be configured via the OTP.
0	INDEPENDENT_ COMPARATOR_ REFERENCE	0	Y	Y	R/W	0: 1.2V 1: 2.1V	Default: 0  This bit sets the independent comparator reference. This bit can be configured via the OTP.



## REG0Dh: System/OTG Under-Voltage and Over-Voltage Setting

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
7	RESERVED	0	N/A	N/A	N/A	Reserved.	Reserved.
6	RESERVED	0	N/A	N/A	N/A	Reserved.	Reserved.
5	Vотс_ov/ Vsys_ov[1]	0	Y	Y	R/W	00: 125% 01: 120%	Default: 00 These bits set the OTG overvoltage (OV) and system OV
4	Vотg_ov/ Vsys_ov[0]	0	Y	Y	R/W	10: 115% 11: 110%	threshold. It is a percentage of the OTG voltage and V <sub>SYS</sub> . These bits can be configured via the OTP.
3	V <sub>OTG_Uv</sub> / Vsys_uv[1]	0	Y	Y	R/W	00: 75% 01: 80% 10: 85%	Default: 00 These bits set the OTG undervoltage lockout (UVLO) voltage and system UVLO voltage. It is
2	Votg_uv/ Vsys_uv[0]	0	Y	Y	R/W	11: 90%	a percentage of the OTG voltage and V <sub>SYS</sub> . These bits can be configured via the OTP.
1	SYS_UV_ PROCHOT[1]	0	Y	Y	R/W	00: 5.6V 01: 5.8V	Default: 01  These bits set the low system
0	SYS_UV_ PROCHOT[0]	1	Y	Y	R/W	10: 6.0V 11: 6.2V	voltage PROCHOT assertion threshold. These bits can be configured via the OTP.

## **REG0Eh: PROCHOT Interrupt Debounce Time and Duration Time Setting**

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
7	tdeb[2]	0	Y	Y	R/W	000: 100μs 001: 200μs	Default: 001  These bits set the time before
6	tdeb[1]	0	Y	Y	R/W	010: 300µs 011: 400µs 100: 500µs 101: 600µs	the following assertions are triggered via PROCHOT: ACProchot, DCProchot, absent input, absent battery, and
5	tdeb[0]	1	Y	Y	R/W	110: 700µs 111: 800µs	independent comparator output. These bits can be configured via the OTP.
4	t <sub>DUR</sub> [3]	0	Υ	Υ	R/W	1600µs.	Default: 400µs
3	t <sub>DUR</sub> [2]	0	Υ	Υ	R/W	800µs.	Offset: 200µs  These bits set the duration time
2	t <sub>DUR</sub> [1]	0	Y	Y	R/W	400µs.	for the PROCHOT signal once it is asserted. These bits can be
1	t <sub>DUR</sub> [0]	1	Y	Y	R/W	200µs.	configured via the OTP.
0	RESERVED	1	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.





# **REG0Fh: Input Current Limit 2 Setting**

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
7	RESERVED	0	N/A	N/A	N/A	Reserved.	Reserved.
6	I <sub>IN_LIM2</sub> [6]	0	Υ	Υ	R/W	3200mA.	
5	I <sub>IN_LIM2</sub> [5]	0	Υ	Υ	R/W	1600mA.	Default: 4.5A
4	I <sub>IN_LIM2</sub> [4]	1	Υ	Υ	R/W	800mA.	Default: 1.5A Range: 0mA to 5A Offset: 0mA
3	I <sub>IN_LIM2</sub> [3]	1	Υ	Υ	R/W	400mA.	These bits set the second I <sub>IN</sub>
2	I <sub>IN_LIM2</sub> [2]	1	Υ	Υ	R/W	200mA.	limit (RS1 = $10m\Omega$ ). These bits can be configured via the
1	I <sub>IN_LIM2</sub> [1]	1	Y	Y	R/W	100mA.	OTP.
0	I <sub>IN_LIM2</sub> [0]	0	Y	Y	R/W	50mA.	

# **REG10h: Input Current Limit 2 Duration Setting**

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
7	t <sub>MAX</sub> [6]	0	Υ	Υ	R/W	12800µs.	
6	t <sub>MAX</sub> [5]	0	Y	Υ	R/W	6400µs.	
5	t <sub>MAX</sub> [4]	0	Y	Υ	R/W	3200µs.	Default: 100µs Range: 100µs to 25.5ms
4	t <sub>MAX</sub> [3]	0	Y	Υ	R/W	1600µs.	Offset: 100µs  These bits set the second I <sub>IN</sub>
3	t <sub>MAX</sub> [2]	0	Y	Υ	R/W	800µs.	limit duration (RS = $10m\Omega$ ). These bits can be configured
2	t <sub>MAX</sub> [1]	0	Y	Υ	R/W	400μs.	via the OTP.
1	t <sub>MAX</sub> [0]	0	Y	Υ	R/W	200µs.	
0	RESERVED	1	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.



## **REG11h: Two-Level Input Current Limit Period Setting**

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
7	t <sub>PERIOD</sub> [6]	1	Υ	Υ	R/W	12800µs.	
6	tperiod[5]	1	Y	Υ	R/W	6400µs.	Default: 1111 111 (25.5ms)
5	tperiod[4]	1	Y	Υ	R/W	3200µs.	Range: 100µs to 25.5ms Offset: 100µs
4	tperiod[3]	1	Y	Υ	R/W	1600µs.	These bits set the total time duration of for the second and
3	tperiod[2]	1	Y	Υ	R/W	800µs.	first $I_{IN}$ limit (RS1 = $10m\Omega$ ). These bits can be configured
2	t <sub>PERIOD</sub> [1]	1	Y	Υ	R/W	400μs.	via the OTP.
1	t <sub>PERIOD</sub> [0]	1	Y	Υ	R/W	200µs.	
0	RESERVED	1	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.

# **REG12h: Input OCP Threshold for Triggering PROCHOT**

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
7	RESERVED	0	N/A	N/A	N/A	Reserved.	Reserved.
6	IIN_OCP[3]	1	Y	Y	R/W	6400mA.	Default: 11.9A Offset: 700mA
5	I <sub>IN_OCP</sub> [2]	1	Υ	Y	R/W	3200mA.	These bits set the input over-
4	IIN_OCP[1]	1	Υ	Y	R/W	1600mA.	current (OC) threshold. PROCHOT is triggered when IIN exceeds this threshold.
3	I <sub>IN_OCP</sub> [0]	0	Y	Y	R/W	800mA.	These bits can be configured via the OTP.
2	RESERVED	1	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
1	DIG_SKIP_ EN	1	Y	Y	R/W	0: Disabled 1: Enabled	When this bit is set to 1, digital skip mode is enabled to skip PWM when the load is light for all loops. This bit can be configured via the OTP.
0	RESERVED	1	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.

© 2022 MPS. All Rights Reserved.





# **REG13h: Status Register**

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
7	BATT_UVLO	0	N/A	N/A	R	0: V <sub>BATT</sub> UVLO has not occurred 1: V <sub>BATT</sub> UVLO has occurred	Default: 0  This bit indicates the VBATT under-voltage lockout (UVLO) status. It is set to 0 by default.
6	VSYS_UV	0	N/A	N/A	R	0: The system does not have a UV condition 1: The system has a UV condition	Default: 0  This bit indicates an under-voltage (UV) condition, which triggers short-circuit protection (SCP).
5	RESERVED	0	N/A	N/A	N/A	Reserved.	Reserved.
4	PPM_STAT	0	N/A	N/A	R	0: No DPM 1: VINDPM or IINDPM	Default: 0  This bit indicates the power path management status.
3	CHG_ STAT[1]	0	N/A	N/A	R	00: Not charging 01: Trickle charging or	Default: 00
2	CHG_ STAT[0]	0	N/A	N/A	R	Pre-charging 10: Fast charging 11: Charge termination	These bits indicate the charging status.
1	ACOK	0	N/A	N/A	R	0: V <sub>IN</sub> not PG 1: V <sub>IN</sub> PG	Default: 0  This bit indicates the power good (PG) status.
0	VSYS_STAT	0	N/A	N/A	R	0: In VSYSMIN regulation 1: Not in VSYSMIN regulation	Default: 0 This bit indicates the VSYS regulation status.





# **REG14h: Fault Register**

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
7	WATCHDOG_ FAULT	0	N/A	N/A	R	0: Normal operation 1: The watchdog timer has expired	Default: 0  This bit indicates whether a watchdog fault has occurred. It is set to 0 by default.
6	OTG_FAULT	0	N/A	N/A	R	0: Normal operation 1: VBUS is overloaded, or VBUS over-voltage protection (OVP) has occurred	Default: 0  This bit indicates whether an OTG mode fault has occurred. It is set to 0 by default.
5	CHG_FAULT [1]	0	N/A	N/A	R	00: Normal operation 01: Input OVP has occurred 10: Thermal shutdown	Default: 00  These bits indicate whether a charge fault
4	CHG_FAULT [0]	0	N/A	N/A	R	has occurred 11: The safety timer has expired	has occurred. They are set to 00 by default.
3	BATT_ FAULT	0	N/A	N/A	R	0: Normal operation 1: Battery OVP has occurred	Default: 0  This bit indicates whether a battery fault has occurred. It is set to 0 by default.
2	NTC_FAULT [2]	0	N/A	N/A	R	000: Normal	Default: 000
1	NTC_FAULT [1]	0	N/A	N/A	R	001: NTC cold 010: NTC cool 011: NTC warm	These bits indicate whether an NTC fault has occurred. They
0	NTC_FAULT [0]	0	N/A	N/A	R	100: NTC hot	are set to 000 by default.





## REG16~17h: ADC Battery Voltage Result

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
15	V <sub>BATT</sub> [9]	N/A	N/A	N/A	R	6400mV.	
14	VBATT[8]	N/A	N/A	N/A	R	3200mV.	
13	VBATT[7]	N/A	N/A	N/A	R	1600mV.	
12	Vватт[6]	N/A	N/A	N/A	R	800mV.	These bits indicate the ADC
11	Vватт[5]	N/A	N/A	N/A	R	400mV.	conversion of V <sub>BATT</sub> .
10	V <sub>BATT</sub> [4]	N/A	N/A	N/A	R	200mV.	For 2 cells: 12.5mV/LSB For 3 cells: 18.75mV/LSB
9	V <sub>BATT</sub> [3]	N/A	N/A	N/A	R	100mV.	For 4 cells: 25mV/LSB
8	V <sub>BATT</sub> [2]	N/A	N/A	N/A	R	50mV.	
7	VBATT[1]	N/A	N/A	N/A	R	25mV.	
6	VBATT[0]	N/A	N/A	N/A	R	12.5mV.	
5	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
4	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
3	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
2	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
1	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
0	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.





# REG18~19h: ADC System Voltage Result

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
15	V <sub>SYS</sub> [9]	N/A	N/A	N/A	R	6400mV.	
14	Vsys[8]	N/A	N/A	N/A	R	3200mV.	
13	Vsys[7]	N/A	N/A	N/A	R	1600mV.	
12	Vsys[6]	N/A	N/A	N/A	R	800mV.	These bits indicate the ADC
11	V <sub>SYS</sub> [5]	N/A	N/A	N/A	R	400mV.	conversion of V <sub>SYS</sub> .
10	V <sub>SYS</sub> [4]	N/A	N/A	N/A	R	200mV.	For 2 cells: 12.5mV/LSB For 3 cells: 18.75mV/LSB
9	V <sub>SYS</sub> [3]	N/A	N/A	N/A	R	100mV.	For 4 cells: 25mV/LSB
8	V <sub>SYS</sub> [2]	N/A	N/A	N/A	R	50mV.	
7	Vsys[1]	N/A	N/A	N/A	R	25mV.	
6	Vsys[0]	N/A	N/A	N/A	R	12.5mV.	
5	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
4	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
3	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
2	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
1	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
0	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.





# REG1A~1Bh: ADC Battery Charge Current Result

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
15	I <sub>CHG</sub> [9]	N/A	N/A	N/A	R	6400mA.	
14	Існд[8]	N/A	N/A	N/A	R	3200mA.	
13	I <sub>CHG</sub> [7]	N/A	N/A	N/A	R	1600mA.	
12	Існс[6]	N/A	N/A	N/A	R	800mA.	
11	I <sub>CHG</sub> [5]	N/A	N/A	N/A	R	400mA.	These bits indicate the ADC
10	I <sub>CHG</sub> [4]	N/A	N/A	N/A	R	200mA.	conversion of I <sub>CHG</sub> .
9	I <sub>CHG</sub> [3]	N/A	N/A	N/A	R	100mA.	
8	I <sub>CHG</sub> [2]	N/A	N/A	N/A	R	50mA.	
7	I <sub>CHG</sub> [1]	N/A	N/A	N/A	R	25mA.	
6	Ichg[0]	N/A	N/A	N/A	R	12.5mA.	
5	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
4	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
3	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
2	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
1	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
0	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.





# REG1C~1Dh: ADC Input Voltage Result

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
15	V <sub>IN</sub> [9]	N/A	N/A	N/A	R	12800mV.	
14	V <sub>IN</sub> [8]	N/A	N/A	N/A	R	6400mV.	
13	V <sub>IN</sub> [7]	N/A	N/A	N/A	R	3200mV.	
12	V <sub>IN</sub> [6]	N/A	N/A	N/A	R	1600mV.	
11	V <sub>IN</sub> [5]	N/A	N/A	N/A	R	800mV.	These bits indicate the
10	V <sub>IN</sub> [4]	N/A	N/A	N/A	R	400mV.	ADC conversion of V <sub>IN</sub> .
9	V <sub>IN</sub> [3]	N/A	N/A	N/A	R	200mV.	
8	V <sub>IN</sub> [2]	N/A	N/A	N/A	R	100mV.	
7	V <sub>IN</sub> [1]	N/A	N/A	N/A	R	50mV.	
6	V <sub>IN</sub> [0]	N/A	N/A	N/A	R	25mV.	
5	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
4	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
3	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
2	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
1	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
0	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.





## **REG1E~1Fh: ADC Input Current Result**

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
15	I <sub>IN</sub> [9]	N/A	N/A	N/A	R	3200mA.	
14	I <sub>IN</sub> [8]	N/A	N/A	N/A	R	1600mA.	
13	I <sub>IN</sub> [7]	N/A	N/A	N/A	R	800mA.	
12	I <sub>IN</sub> [6]	N/A	N/A	N/A	R	400mA.	
11	I <sub>IN</sub> [5]	N/A	N/A	N/A	R	200mA.	These bits indicate the
10	I <sub>IN</sub> [4]	N/A	N/A	N/A	R	100mA.	ADC conversion of I <sub>IN</sub> .
9	I <sub>IN</sub> [3]	N/A	N/A	N/A	R	50mA.	
8	I <sub>IN</sub> [2]	N/A	N/A	N/A	R	25mA.	
7	I <sub>IN</sub> [1]	N/A	N/A	N/A	R	12.5mA.	
6	I <sub>IN</sub> [0]	N/A	N/A	N/A	R	6.25mA.	
5	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
4	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
3	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
2	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
1	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
0	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.





## REG20~21h: ADC OTG Output Voltage Result

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
15	V <sub>IN_OTG</sub> [9]	N/A	N/A	N/A	R	12800mV.	
14	VIN_OTG[8]	N/A	N/A	N/A	R	6400mV.	
13	VIN_OTG[7]	N/A	N/A	N/A	R	3200mV.	
12	VIN_OTG[6]	N/A	N/A	N/A	R	1600mV.	
11	V <sub>IN_OTG</sub> [5]	N/A	N/A	N/A	R	800mV.	These bits indicate the ADC conversion of the
10	V <sub>IN_OTG</sub> [4]	N/A	N/A	N/A	R	400mV.	OTG voltage.
9	V <sub>IN_OTG</sub> [3]	N/A	N/A	N/A	R	200mV.	
8	V <sub>IN_OTG</sub> [2]	N/A	N/A	N/A	R	100mV.	
7	V <sub>IN_OTG</sub> [1]	N/A	N/A	N/A	R	50mV.	
6	VIN_OTG[0]	N/A	N/A	N/A	R	25mV.	
5	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
4	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
3	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
2	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
1	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
0	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.





## REG22~23h: ADC OTG Output Current Result

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
15	I <sub>ОТG</sub> [9]	N/A	N/A	N/A	R	3200mA.	
14	Іотд[8]	N/A	N/A	N/A	R	1600mA.	
13	lотg[ <b>7</b> ]	N/A	N/A	N/A	R	800mA.	
12	Іотс[6]	N/A	N/A	N/A	R	400mA.	
11	Іотс[5]	N/A	N/A	N/A	R	200mA.	These bits indicate the
10	I <sub>OTG</sub> [4]	N/A	N/A	N/A	R	100mA.	ADC conversion of the OTG current.
9	I <sub>OTG</sub> [3]	N/A	N/A	N/A	R	50mA.	
8	I <sub>OTG</sub> [2]	N/A	N/A	N/A	R	25mA.	
7	l <sub>от</sub> [1]	N/A	N/A	N/A	R	12.5mA.	
6	Іотс[0]	N/A	N/A	N/A	R	6.25mA.	
5	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
4	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
3	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
2	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
1	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
0	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.





# REG24~25h: ADC Junction Temperature Result

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
15	TJ[9]	N/A	N/A	N/A	R	512.	
14	TJ[8]	N/A	N/A	N/A	R	256.	
13	TJ[7]	N/A	N/A	N/A	R	128.	
12	TJ[6]	N/A	N/A	N/A	R	64.	These bits indicate the ADC conversion of the
11	TJ[5]	N/A	N/A	N/A	R	32.	IC's junction temperature (T <sub>J</sub> ). T <sub>J</sub> can be calculated
10	TJ[4]	N/A	N/A	N/A	R	16.	with the following equation:
9	TJ[3]	N/A	N/A	N/A	R	8.	T <sub>J</sub> = 903 - 2.578 x T (°C)
8	TJ[2]	N/A	N/A	N/A	R	4.	
7	TJ[1]	N/A	N/A	N/A	R	2.	
6	TJ[0]	N/A	N/A	N/A	R	1.	
5	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
4	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
3	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
2	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
1	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
0	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.





## REG26~27h: ADC System Power Result

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
15	P <sub>SYS</sub> [9]	N/A	N/A	N/A	R	64W.	
14	Psys[8]	N/A	N/A	N/A	R	32W.	
13	P <sub>SYS</sub> [7]	N/A	N/A	N/A	R	16W.	
12	Psys[6]	N/A	N/A	N/A	R	8W.	
11	P <sub>SYS</sub> [5]	N/A	N/A	N/A	R	4W.	These bits indicate the ADC conversion of the
10	P <sub>SYS</sub> [4]	N/A	N/A	N/A	R	2W.	system power.
9	P <sub>SYS</sub> [3]	N/A	N/A	N/A	R	1W.	
8	Psys[2]	N/A	N/A	N/A	R	0.5W.	
7	P <sub>SYS</sub> [1]	N/A	N/A	N/A	R	0.25W.	
6	Psys[0]	N/A	N/A	N/A	R	0.125W.	
5	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
4	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
3	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
2	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
1	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
0	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.





# REG28~29h: ADC Battery Discharge Current Result

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
15	I <sub>BATT_DSG</sub> [9]	N/A	N/A	N/A	R	6400mA.	
14	IBATT_DSG[8]	N/A	N/A	N/A	R	3200mA.	
13	IBATT_DSG[7]	N/A	N/A	N/A	R	1600mA.	
12	IBATT_DSG[6]	N/A	N/A	N/A	R	800mA.	
11	IBATT_DSG[5]	N/A	N/A	N/A	R	400mA.	These bits indicate the ADC conversion of the
10	I <sub>BATT_DSG</sub> [4]	N/A	N/A	N/A	R	200mA.	battery discharge current.
9	I <sub>BATT_DSG</sub> [3]	N/A	N/A	N/A	R	100mA.	
8	I <sub>BATT_DSG</sub> [2]	N/A	N/A	N/A	R	50mA.	
7	IBATT_DSG[1]	N/A	N/A	N/A	R	25mA.	
6	IBATT_DSG[0]	N/A	N/A	N/A	R	12.5mA.	
5	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
4	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
3	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
2	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
1	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
0	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.



# **REG2Bh: Battery OVP Deglitch Time**

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
7	RESERVED	0	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
6	RESERVED	0	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
5	RESERVED	0	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
4	RESERVED	0	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
3	RESERVED	0	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
2	RESERVED	0	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
1	RESERVED	0	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
0	VBATT_OVP _DGL	1	Y	Y	R/W	0: 200μs 1: 1μs	Default: 1 This bit can be configured via the OTP.

## **REG2Dh: Battery Voltage Loop Enable**

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
7	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
6	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
5	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
4	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
3	RESERVED	0	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
2	RESERVED	0	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
1	RESERVED	1	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
0	VBATT_LP_ EN	1	Υ	Υ	R/W	0: Disabled 1: Enabled	This bit can be configured via the OTP.



## **REG30h: Battery Pre-Charge Threshold Option**

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
7	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
6	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
5	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
4	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
3	VBATT_PRE_ SEL	0	Y	Y	R/W	0: Option 1 1: Option 2	Default: 0 This bit can be configured via the OTP.
2	RESERVED	1	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
1	RESERVED	0	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
0	RESERVED	0	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.

#### **REG31h: System Voltage Threshold for Pulse Skipping**

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment	
7	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.	
6	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.	
5	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.	
4	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.	
3	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.	
2	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.	
1	VSYS_ SKIP [1]	0	Y	Y	R/W	00: 102% 01: 103%	Default: 00	
0	VSYS_ SKIP[0]	0	Υ	Y	R/W	10: 104% 11: 101%	These bits can be configured via the OTP.	



## REG33h: INT Mask for Hi-Z Mode Entry and Exit

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
7	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
6	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
5	RESERVED	0	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
4	RESERVED	1	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
3	RESERVED	0	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
2	HIZ_INT_ MASK	1	Y	Y	R/W	0: Masked 1: Not masked	Default: 1  This bit configures the INT output for Hi-Z mode entry and exit. This bit can be configured via the OTP.
1	RESERVED	0	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
0	RESERVED	1	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.

## **REG36h: Analog Frequency Loop Enable**

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
7	RESERVED	1	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
6	RESERVED	1	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
5	RESERVED	0	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
4	RESERVED	1	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
3	RESERVED	0	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
2	RESERVED	1	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.
1	FS_LOOP_ EN	0	Y	Y	R/W	0: Disabled 1: Enabled	This bit enables the analog frequency loop. When the loop is disabled, an alternative tope calculation calibrates fsw. This bit can be configured via the OTP.
0	RESERVED	1	N/A	N/A	N/A	Reserved.	Internal use only. Do not change the value of this bit.



## REG40~41h: ADC Result for NTC Voltage

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment				
15	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.				
14	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.				
13	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.				
12	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.				
11	NTC[11]	N/A	N/A	N/A	R	2048.					
10	NTC[10]	N/A	N/A	N/A	R	1024.					
9	NTC[9]	N/A	N/A	N/A	R	512.					
8	NTC[8]	N/A	N/A	N/A	R	256.					
7	NTC[7]	N/A	N/A	N/A	R	128.	These bits indicate the ADC conversion of the				
6	NTC[6]	N/A	N/A	N/A	R	64.	NTC voltage vs. the reference voltage (1.6V).				
5	NTC[5]	N/A	N/A	N/A	R	32.	The real NTC voltage can be calculated with the				
4	NTC[4]	N/A	N/A	N/A	R	16.	following equation: NTC[11:0] x 1.6V / 4096				
3	NTC[3]	N/A	N/A	N/A	R	8.					
2	NTC[2]	N/A	N/A	N/A	R	4.					
1	NTC[1]	N/A	N/A	N/A	R	2.					
0	NTC[0]	N/A	N/A	N/A	R	1.					

# REG48h: Hi-Z Mode Indication (DC/DC Switcher is Off)

Bit	Name	Default	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
7	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
6	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
5	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
4	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
3	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
2	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
1	RESERVED	N/A	N/A	N/A	N/A	Reserved.	Reserved.
0	HI-Z_MODE	0	N/A	N/A	R	0: Buck charge or boost charge mode 1: Hi-Z mode	This bit indicates the status of the DC/DC stage.



#### APPLICATION INFORMATION

#### Selecting the Input Current-Sense Filter

The MP2650 has an  $I_{\rm IN}$  loop that limits the output current drawn from the USB port. An external current-sense resistor is required to sense the average  $I_{\rm IN}$ . The  $I_{\rm IN}$  value sensed through IAP and IAN covers the ripple current and improves the  $I_{\rm IN}$  accuracy and loop stability.

Figure 19 shows a recommended application that can filter noise.

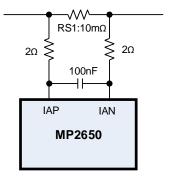


Figure 19: Input Current-Sense Filter

#### **Selecting the Input Capacitor**

The input capacitor from the typical application circuit absorbs the maximum ripple current from the PWM converter (see Figure 23 on page 63). The worst-case RMS ripple current is half of the output current when the duty cycle is 50% in

buck mode. The RMS ripple current can be estimated with Equation (5):

$$I_{\text{CIN\_RMS}} = I_{\text{SYS}} x \frac{\sqrt{V_{\text{SYS}} x (V_{\text{IN}} - V_{\text{SYS}})}}{V_{\text{IN}}}$$
 (5)

Low-ESR ceramic capacitors with X7R or X5R dielectrics are recommended to be the input decoupling capacitor, and should be placed as close as possible to IN and PGND. Their voltage rating must exceed the normal V<sub>IN</sub> level. A capacitor with a minimum 25V rating is recommended for applications with a 20V V<sub>IN</sub>.

#### Selecting the VMAX\_BST Output Capacitor

The MP2650 has an integrated charge pump to power the HS-FET driver. An external output capacitor must be placed between the VMAX\_BST pin and PGND to act as an output capacitor for the integrated charge pump. In addition to the charge pump output, several other paths can supplement the output capacitor (see Figure 20). To limit the inrush current flowing into the capacitor during input power or battery hot insertion, place an additional  $100\Omega$  resistor in series with the charge pump output capacitor.

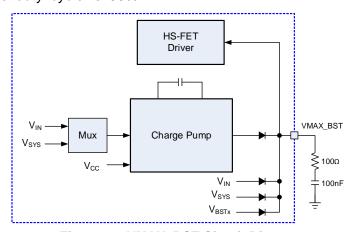


Figure 20: VMAX\_BST Circuit Diagram

#### **VCC Decoupling Capacitor**

VCC is an internal LDO output. An external  $10\mu F$  decoupling capacitor must be placed between VCC and AGND.

#### **INT and PROCHOT Pull-Up**

Both the INT and PROCHOT pins are opendrain outputs that interrupt operation if any status or faults occurs. To deliver high logic, these pins must be pulled up to an external power source with  $10k\Omega$  to  $100k\Omega$  resistors.



#### **NTC Sense Resistor Divider**

In real applications, an external NTC thermistor must be placed close to the battery to sense the battery's temperature. The MP2650 measures the battery temperature by monitoring the

voltage ratio between the NTC and VNTC pins Figure 21). Every temperature corresponds to a voltage ratio. The MP2650 has four temperature thresholds to satisfy JEITA requirements.

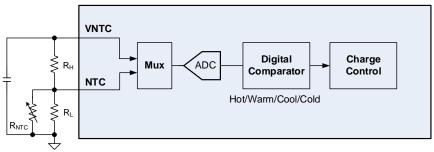


Figure 21: Temperature Sensing

For a given NTC thermistor, the NTC hot and cold temperature points can be calculated with Equation (6) and Equation (7), respectively:

$$\frac{\frac{R_{L}xR_{NTC\_HOT}}{R_{L} + R_{NTC\_HOT}}}{R_{H} + \frac{R_{L}xR_{NTC\_HOT}}{R_{L} + R_{NTC\_HOT}}} = \frac{V_{HOT}}{V_{VNTC}}$$
(6)

$$\frac{\frac{R_{L}xR_{NTC\_COLD}}{R_{L} + R_{NTC\_COLD}}}{R_{H} + \frac{R_{L}xR_{NTC\_COLD}}{R_{L} + R_{NTC\_COLD}}} = \frac{V_{COLD}}{V_{VNTC}}$$
(7)

Where R<sub>NTC HOT</sub> is the thermistor value at the expected hot temperature protection point, and R<sub>NTC COLD</sub> is the thermistor value at the expected cold temperature protection point.

 $V_{\text{HOT}}$  /  $V_{\text{VNTC}}$  and  $V_{\text{COLD}}$  /  $V_{\text{VNTC}}$  are 48.3% and 71.1%, respectively.

Assume the expected hot and cold temperature thresholds are 60°C and 0°C. Using a 104AT thermistor as an example, the thermistor values are:

- $R_{NTC,COLD} = 390.3k\Omega$
- RNTC HOT =  $19.72k\Omega$

R<sub>H</sub> and R<sub>L</sub> can be calculated with Equation (6) and Equation (7). In this scenario,  $R_H$  = 13.79kΩ and  $R_1 = 37.15kΩ$ .

#### Selecting the Inductor

Inductor selection is a tradeoff between cost, size, and efficiency. A lower-value inductor offers a smaller size, but results in higher ripple current, magnetic hysteresis loss, and required output capacitance. The inductor ripple current should not exceed 30% of the maximum load current under the worst-case conditions.

The MP2650 has three options for f<sub>SW</sub>. A higher f<sub>SW</sub> allows for the use of lower-value inductors and capacitors. The inductor saturation current should exceed the load current plus half the ripple current. The recommended inductors are based on a 50% current ripple.

The inductor ripple current in buck operation depends on V<sub>IN</sub>, f<sub>SW</sub>, the duty cycle, and inductance. The inductance (L) can estimated with Equation (8):

$$L = \frac{V_{IN} - V_{SYS}}{\Delta I_I} \times \frac{V_{SYS}}{V_{IN} \times f_{SW}}$$
 (8)

The peak inductor current (IPEAK) can be calculated with Equation (9):

$$I_{PEAK} = I_{LOAD(MAX)} + \frac{\Delta I_{L}}{2}$$
 (9)

Where V<sub>IN</sub> is the input voltage, V<sub>SYS</sub> is the system voltage, f<sub>SW</sub> is the switching frequency, and  $\Delta I_{L}$  is the expected inductor current ripple.

Table 2 on page 61 lists how to select the inductance based on different voltages in buck mode.

Specs	Inductance Selection								
V <sub>IN</sub>	Calculations	L <sub>MIN</sub>	L	Isat	DCR (mΩ)				
9V	I - VIN-VSYS V VSYS	0.65µH	1.5µH	>6.7	<20				
12V	$L = \frac{\Delta I_{L}}{\Delta I_{L}} \times \frac{\delta + \delta}{V_{IN}} \times \frac{\delta + \delta}{V_{SW}}$	1.2µH	1.5µH	>7.1	<20				
15V	$\Delta I_L = 0.5 \times I_{SYS} = 3A$	1.5µH	1.5µH	>7.5	<20				
20V	$f_{SW} = 800kHz$	2.0µH	2.2µH	>7.4	<20				

Table 2: Inductances for Buck Mode

When the MP2650 operates in boost mode, the required inductance (L) can be estimated with Equation (10):

$$L = \frac{V_{IN}x(V_{SYS} - V_{IN})}{V_{SYS}xf_{SW}x\Delta I_L}$$
 (10)

The peak inductor current ( $I_{PEAK}$ ) can be estimated with Equation (11):

$$I_{PEAK} = I_{IN(MAX)} + \frac{\Delta I_{L}}{2}$$
 (11)

Table 3 lists how to select the inductance based on different voltages in boost mode.

**Table 3: Inductances for Boost Mode** 

Specs	Inductance Selection								
Vin	Calculations	L <sub>MIN</sub>	L	Isat	DCR (mΩ)				
5V	$L = \frac{V_{IN}x(V_{SYS} - V_{IN})}{V_{SYS}xf_{SW}x\Delta I_{L}}$ $\Delta I_{L} = 0.5 \times I_{IN} = 2.5A$ $f_{SW} = 800kHz$	1.1µH	1.5µH	>7	<20				

A 1.5µH inductor with a >7.5A saturation current is recommended for most specifications. However, for applications that allow for a higher ripple current, a lower-value inductor can be used to reduce PCB size.

#### Selecting the System Capacitor

The system output capacitor ( $C_{SYS}$ ) from the typical application circuit is parallel to the SYS load (see Figure 23 on page 63).  $C_{SYS}$  absorbs the high-frequency switching ripple current and smooths the output voltage. Its impedance must be below that of the system load to ensure that it absorbs the ripple current.

Ceramic capacitors are recommended for their low ESR and small size, which allows the ESR of the output capacitor to be ignored.

The output voltage ripple can be estimated with Equation (12):

$$\frac{\Delta V_{\text{SYS}}}{V_{\text{SYS}}} = \frac{1 - \frac{V_{\text{SYS}}}{V_{\text{IN}}}}{8xC_{\text{SYS}}xf_{\text{SW}}^2xL}$$
(12)

The maximum output voltage ripple occurs at the minimum  $V_{\text{SYS}}$  and the maximum  $V_{\text{IN}}$ . Assume that a  $\pm 0.2\%$  output ripple voltage should be obtained in CCM.

 $C_{SYS}$  can be estimated with Equation (13):

$$C_{SYS} = \frac{1 - \frac{V_{SYS}}{V_{IN}}}{8xf_{SW}^2 xLx \frac{\Delta V_{SYS}}{V_{SYS}}}$$
(13)

Based on Equation (13),  $C_{SYS}$  must be  $44\mu F$ .

To further improve loop stability, use a minimum 60µF capacitor. For an output capacitor, the recommended ceramic capacitor is 25V, with X7R or X5R dielectrics.



#### **PCB Layout Guidelines**

Efficient PCB layout is critical for specified noise, efficiency, and stability requirements. A minimum 4-layer PCB is recommended to improve thermal performance. For the best results, refer to Figure 22 and follow the guidelines below:

- 1. Connect the VMAX\_BST capacitor to PGND. Place one  $100\Omega$  resistor in series with the VMAX\_BST capacitor.
- 2. Connect AGND to PGND to each decoupling capacitor via a single-point connection.

- 3. Place a 470nF capacitor between the CP1 and CP2 pins.
- 4. Place the VCC capacitor close to the VCC and AGND pins.
- 5. Use a Kelvin connection for the input current-sense resistor.
- 6. Place capacitors between VIN and PGND as close as possible to the pins.
- 7. For the input current sense, use CM and DM filters.

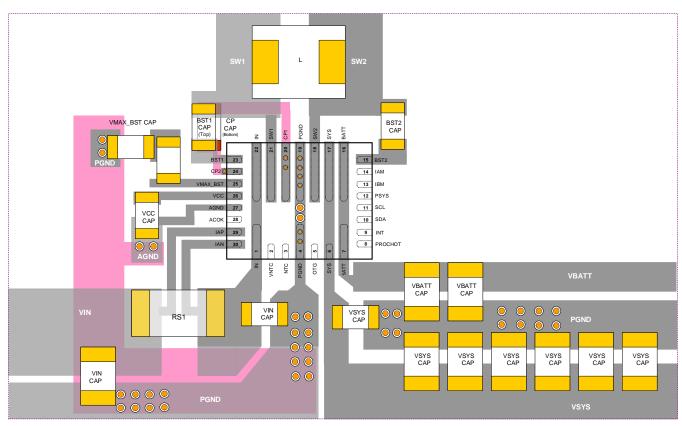
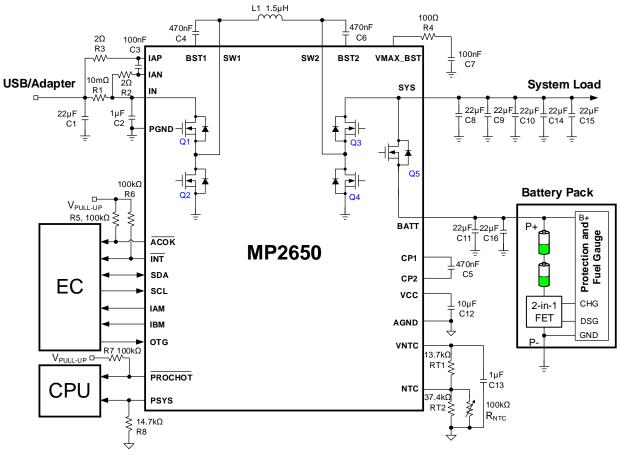


Figure 22: Recommended PCB Layout



#### TYPICAL APPLICATION CIRCUIT



**Figure 23: Typical Application Circuit** 

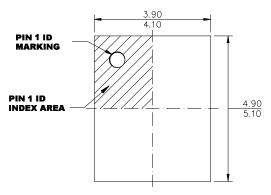
Table 4: Key BOM for Figure 23

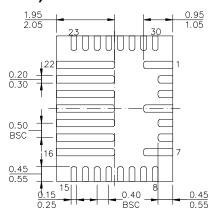
Qty	Ref	Value	Description	Package	Manufacturer
8	C1, C8, C9, C10, C11, C14, C15, C16	22µF	Ceramic capacitor, 25V, X5R or X7R	0805	Any
1	C2	1µF	Ceramic capacitor, 25V, X5R or X7R	0603	Any
1	C3	100nF	Ceramic capacitor, 25V, X5R or X7R	0603	Any
3	C4, C5, C6	470nF	Ceramic capacitor, 25V, X5R or X7R	0603	Any
1	C7	100nF	Ceramic capacitor, 50V, X5R or X7R	0603	Any
1	C12	10µF	Ceramic capacitor, 25V, X5R or X7R	0603	Any
1	R1	10mΩ	Film resistor, 1%	1206	Any
2	R2, R3	2Ω	Film resistor, 1%	0603	Any
1	R4	100Ω	Film resistor, 1%	0603	Any
1	RT1	13.7kΩ	Film resistor, 1%	0603	Any
1	RT2	37.4kΩ	Film resistor, 1%	0603	Any
1	L1	1.5µH	Inductor, 1.5µH, low DCR, I <sub>SAT</sub> > 7A	SMD	Any



#### **PACKAGE INFORMATION**

# **QFN-30 (4mmx5mm)**



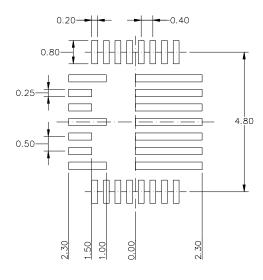


#### **TOP VIEW**

**BOTTOM VIEW** 



**SIDE VIEW** 



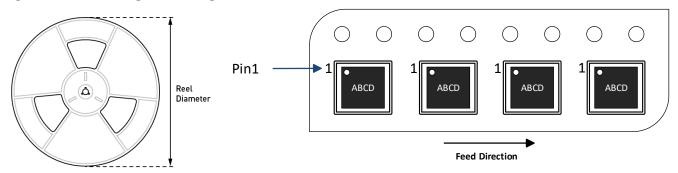
**RECOMMENDED LAND PATTERN** 

#### **NOTE:**

- 1) LAND PATTERN OF PIN1,4 AND PIN7 HAVE THE SAME LENGTH AND WIDTH.
- 2) LAND PATTERN OF PIN16~22 HAVE THE SAME LENGTH AND WIDTH.
- 3) ALL DIMENSIONS ARE IN MILLIMETERS.
- 4) LEAD COPLANARITY SHALL BE 0.08 MILLIMETERS MAX.
- 5) JEDEC REFERENCE IS MO-220.
- 6) DRAWING IS NOT TO SCALE.



# **CARRIER INFORMATION**



Part Number	Package Description	Quantity/ Reel	Quantity/ Tube	Quantity/ Tray	Reel Diameter	Carrier Tape Width	Carrier Tape Pitch
MP2650GV- xxxx-Z	QFN-30 (4mmx5mm)	5000	N/A	N/A	13in	12mm	8mm



#### **REVISION HISTORY**

Revision #	Revision Date	Description	Pages Updated
1.0	4/22/2022	Initial Release	-

Notice: The information in this document is subject to change without notice. Users should warrant and guarantee that thirdparty Intellectual Property rights are not infringed upon when integrating MPS products into any application. MPS will not assume any legal responsibility for any said applications.